Preliminary Datasheet





RL78/G1A

RENESAS MCU

R01DS0151EJ0001 Rev.0.01 2011.12.26

Combines Multi-channel 12-Bit A/D Converter, True Low Power Platform (as low as 66 μ A/MHz, and 0.57 μ A for RTC + LVD), 1.6 V to 3.6 V operation, 16 to 64 Kbyte Flash, 41 DMIPS at 32 MHz

1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 1.6 V to 3.6 V operation from a single supply
- Stop (RAM retained): 0.23 μA, (LVD enabled): 0.31 μA
- Halt (RTC + LVD): 0.57 μA
- Snooze: T.B.D.
- Operating: 66 μA/MHz

16-bit RL78 CPU Core

- Delivers 41 DMIPS at maximum operating frequency of 32 MHz
- Instruction Execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC Architecture (Harvard) with 3-stage pipeline
- Multiply Signed & Unsigned: 16 x 16 to 32-bit result in 1 clock cycle
- MAC: 16 x 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Code Flash Memory

- Density: 16 KB to 64 KB
- Block size: 1 KB
- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory

- Data Flash with background operation
- Data flash size: 4 KB
- Erase Cycles: 1 Million (typ.)
- Erase/programming voltage: 1.8 V to 3.6 V

RAM

- 2 KB to 4 KB size options
- Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator

- \bullet 32 MHz with +/- 1% accuracy over voltage (1.8 V to 3.6 V) and temperature (-20 °C to +85 °C)
- Pre-configured settings: 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 4 MHz & 1 MHz

Reset and Supply Management

- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 12 setting options (Interrupt and/or reset function)

Data Memory Access (DMA) Controller

- Up to 2 fully programmable channels
- Transfer unit: 8- or 16-bit

Multiple Communication Interfaces

- Up to 6 x I2C master
- Up to 1 x I2C multi-master
- Up to 6 x CSI/SPI (7-, 8-bit)
- Up to 3 x UART (7-, 8-, 9-bit)
- Up to 1 x LIN

Extended-Function Timers

- Multi-function 16-bit timers: Up to 8 channels
- Real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- Interval Timer: 12-bit, 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Rich Analog

- ADC: Up to 28 channels, 12-bit resolution, 3.375 μs conversion time
- Supports 1.6 V
- Internal voltage reference (1.45 V)
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)

- Flash memory CRC calculation
- RAM parity error check
- RAM write protection
- SFR write protection
- Illegal memory access detection
- · Clock stop/ frequency detection
- ADC self-test

General Purpose I/O

- 3.6 V tolerant, high-current (up to 20 mA per pin)
- Open-Drain, Internal Pull-up support

Operating Ambient Temperature

• Standard: -40 °C to +85 °C

Package Type and Pin Count

From 3 mm x 3 mm to 10 mm x 10 mm

QFP: 48, 64 QFN: 32, 48 LGA: 25 BGA: 64

1. OUTLINE

O ROM, RAM capacities

Flash	Data	RAM		RL78	3/G1A	
ROM	flash		25 pins	32 pins	48 pins	64 pins
64 KB	4 KB	4 KB Note	R5F10E8E	R5F10EBE	R5F10EGE	R5F10ELE
48 KB	4 KB	3 KB	R5F10E8D	R5F10EBD	R5F10EGD	R5F10ELD
32 KB	4 KB	2 KB	R5F10E8C	R5F10EBC	R5F10EGC	R5F10ELC
16 KB	4 KB	2 KB	R5F10E8A	R5F10EBA	R5F10EGA	_

Note This is about 3 KB when the self-programming function and data flash function are used.

1.2 Ordering Information

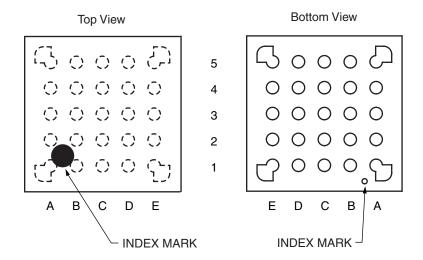
• Flash memory version (lead-free product)

Pin count	Package	Data flash	Part Number
25 pins	25-pin plastic FLGA (3 × 3)	Mounted	R5F10E8AALA, R5F10E8CALA, R5F10E8DALA, R5F10E8EALA
32 pins	32-pin plastic WQFN (fine pitch) (5 × 5)	Mounted	R5F10EBAANA, R5F10EBCANA, R5F10EBDANA, R5F10EBEANA
48 pins	48-pin plastic LQFP (fine pitch) (7 × 7)	Mounted	R5F10EGAAFB, R5F10EGCAFB, R5F10EGDAFB, R5F10EGEAFB
	48-pin plastic WQFN (7 × 7)	Mounted	R5F10EGAANA, R5F10EGCANA, R5F10EGDANA, R5F10EGEANA
64 pins	64-pin plastic LQFP (fine pitch) (10 × 10)	Mounted	R5F10ELCAFB, R5F10ELDAFB, R5F10ELEAFB
	64-pin plastic FBGA (4 × 4)	Mounted	R5F10ELCABG, R5F10ELDABG, R5F10ELEABG

1.3 Pin Configuration (Top View)

1.3.1 25-pin products

• 25-pin plastic FLGA (3 × 3)



	Α	В	С	D	E	
5	P40/TOOL0	RESET	P03/ANI16/ RxD1/TO00/ (KR1)	P23/ANI3/ (KR3)	AVss	5
4	P122/X2/ EXCLK	P137/INTP0	P02/ANI17/ TxD1/TI00/ (KR0)	P22/ANI2/ (KR2)	AV _{DD}	4
3	P121/X1	V _{DD}	P21/ANI1/ AVREFM	P11/ANI20/ SI00/SDA00/ RxD0/ TOOLRxD	P10/ANI18/ SCK00/SCL00	3
2	REGC	Vss	P30/ANI27/ SCK11/SCL11/ INTP3	P51/ANI25/ SO11/INTP2	P50/ANI26/ SI11/SDA11 INTP1	2
1	P60/SCLA0	P61/SDAA0	P31/ANI29/TI03/ TO03/PCLBUZ0 /INTP4	P12/ANI21/ SO00/TxD0/ TOOLTxD	P20/ANI0/ AVREFP	1
	A	В	С	D	E	•

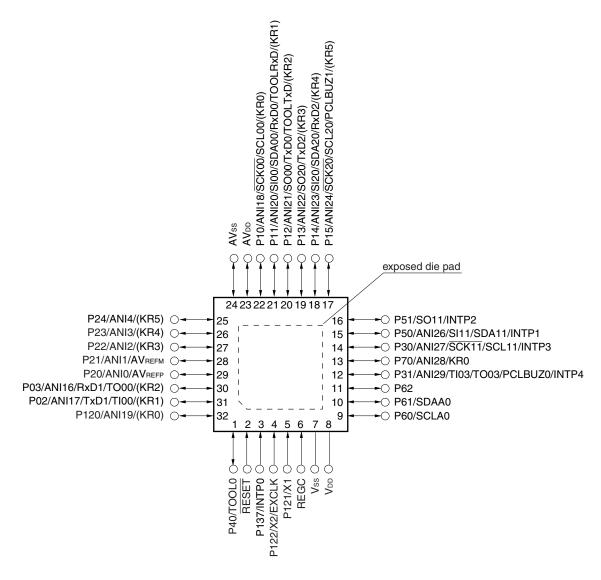
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.2 32-pin products

• 32-pin plastic WQFN (fine pitch) (5 × 5)



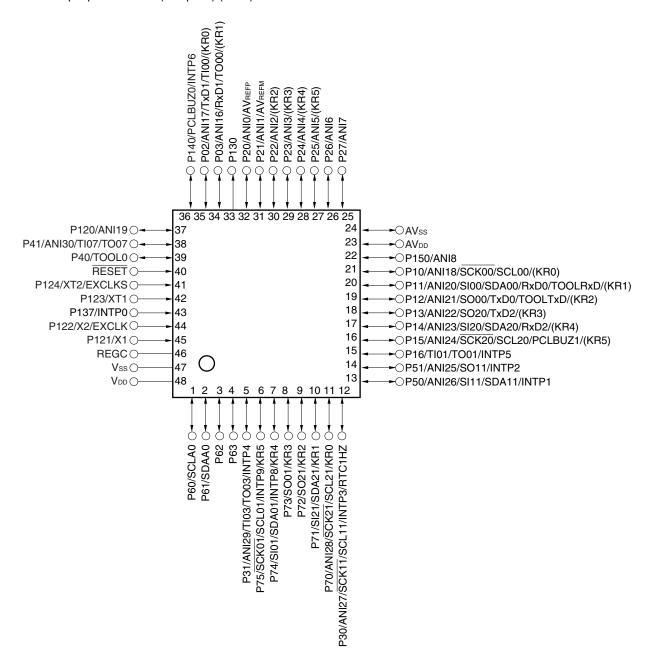
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.3 48-pin products

• 48-pin plastic LQFP (fine pitch) (7 × 7)

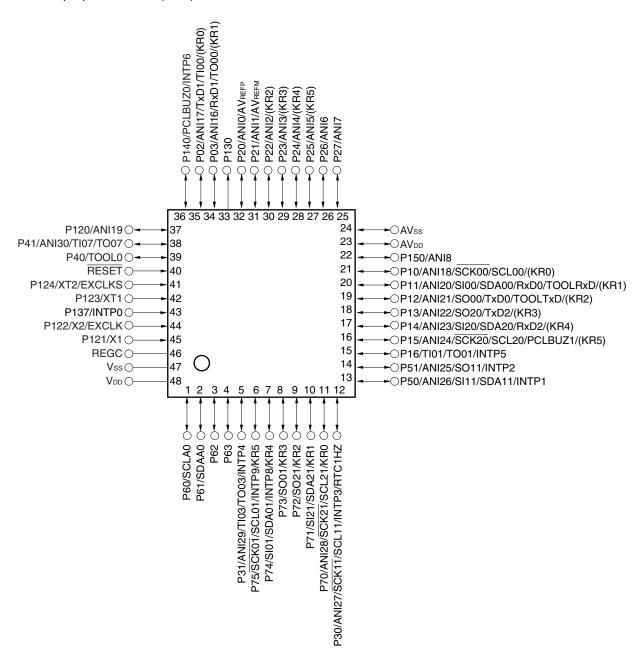


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

• 48-pin plastic WQFN (7 × 7)



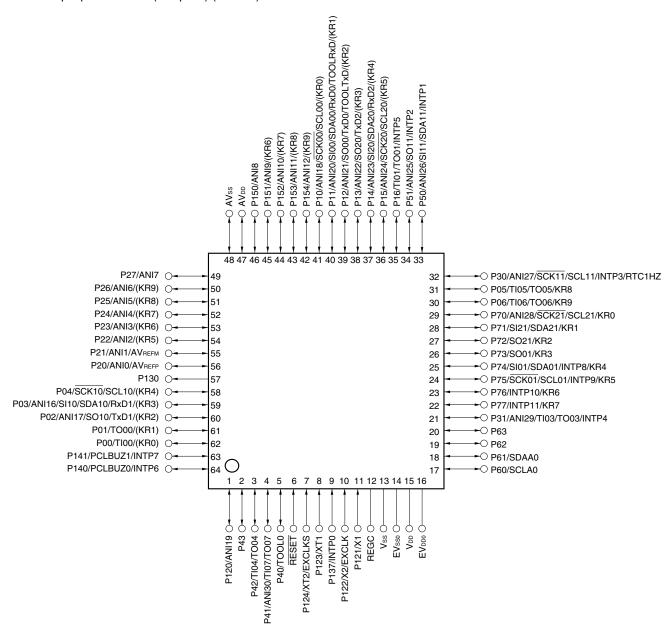
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

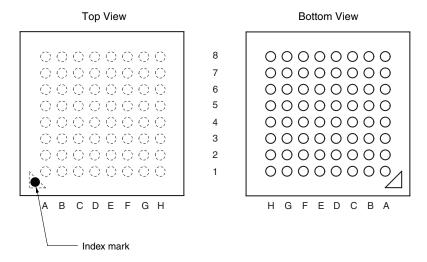
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• 64-pin plastic LQFP (fine pitch) (10 × 10)



- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is higher than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDDO pins and connect the Vss and EVss0pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

• 64-pin plastic FBGA (4 × 4)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05/KR8	C1	P51/ANI25/SO11 /INTP2	E1	P153/ANI11/(KR8)	G1	AV _{DD}
A2	P30/ANI27/SCK11 /SCL11/INTP3 /RTC1HZ	C2	P71/SI21/SDA21/KR1	E2	P154/ANI12/(KR9)	G2	P25/ANI5/(KR8)
A3	P70/ANI28/SCK21 /SCL21/KR0	C3	P74/SI01/SDA01 /INTP8/KR4	E3	P10/ANI18/SCK00 /SCL00/(KR0)	G3	P24/ANI4/(KR7)
A4	P75/SCK01/SCL01 /INTP9/KR5	C4	P16/TI01/TO01/INTP5	E4	P11/ANI20/SI00 /SDA00/RxD0 /TOOLRxD/(KR1)	G4	P22/ANI2/(KR5)
A5	P77/INTP11/KR7	C5	P15/ANI24/SCK20 /SCL20/(KR5)	E5	P03/ANI16/SI10 /SDA10/RxD1/(KR3)	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/ANI30/TI07/TO07	G6	P02/ANI17/SO10/TxD1 /(KR2)
A7	P60/SCLA0	C7	Vss	E7	RESET	G7	P00/TI00/(KR0)
A8	EV _{DD0}	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/ANI26 /SI11 /SDA11/INTP1	D1	P13/ANI22/SO20 /TxD2/(KR3)	F1	P150/ANI8	H1	AVss
B2	P72/SO21/KR2	D2	P06/TI06/TO06/KR9	F2	P151/ANI9/(KR6)	H2	P27/ANI7
В3	P73/S001/KR3	D3	P12/ANI21/SO00 /TxD0/TOOLTxD/(KR2)	F3	P152/ANI10/(KR7)	НЗ	P26/ANI6/(KR9)
B4	P76/INTP10/KR6	D4	P14/ANI23/SI20/ SDA20/RxD2/(KR4)	F4	P21/ANI1/AVREFM	H4	P23/ANI3/(KR6)
B5	P31/ANI29/TI03/TO03 /INTP4	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10 /(KR4)	H5	P20/ANI0/AVREFP
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V _{DD}	D7	REGC	F7	P01/TO00/(KR1)	H7	P140/PCLBUZ0/INTP6
B8	EVsso	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is higher than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EV_{DD0} pins and connect the Vss and EV_{SS0} pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

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1. OUTLINE

1.4 Pin Identification

ANI0 to ANI12, PCLBUZ0, PCLBUZ1: Programmable clock output/buzzer ANI16 to ANI30: Analog input output AV_{DD}: REGC: Regulator capacitance Analog power supply AVss: Analog ground RESET: Reset AVREFM: A/D converter reference RTC1HZ: Real-time clock correction clock potential (- side) input (1 Hz) output AVREFP: A/D converter reference RxD0 to RxD2: Receive data potential (+ side) input SCK00, SCK01, SCK10, EV_{DD0}: Power supply for port SCK11, SCK20, SCK21: Serial clock input/output EVsso: Ground for port SCLA0, SCL00, SCL01, EXCLK: External clock input (main SCL10, SCL11, SCL20, SCL21: system clock) Serial clock input/output External clock input (sub **EXCLKS:** SDAA0, SDA00, SDA01, system clock) SDA10, SDA11, SDA20, INTP0 to INTP11: External interrupt input SDA21: Serial data input/output KR0 to KR9: Key return SI00, SI01, SI10, SI11, P00 to P06: Port 0 SI20, SI21: Serial data input P10 to P16: Port 1 SO00, SO01, SO10, P20 to P27: Port 2 SO11, SO20, SO21: Serial data output P30, P31: Port 3 TI00, TI01, TI03 to TI07: Timer input P40 to P43: Port 4 TO00, TO01, P50, P51: TO03 to TO07: Port 5 Timer output P60 to P63: Port 6 TOOL0: Data input/output for tool P70 to P77: Port 7 TOOLRxD, TOOLTxD: Data input/output for external device

P120 to P124: Port 12 TxD0 to TxD2: Transmit data

P130, P137: Port 13 VDD: Power supply

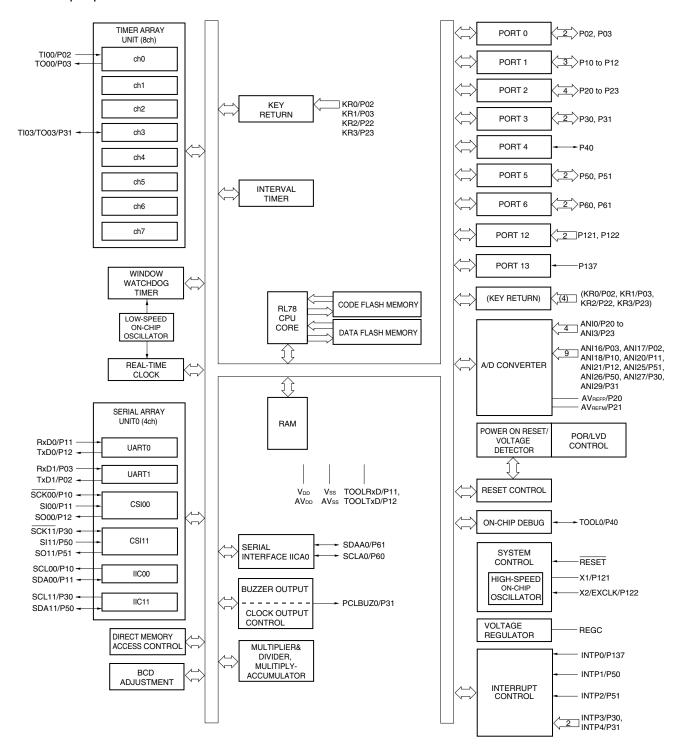
P140, P141: Port 14 Vss: Ground
P150 to P154: Port 15 X1, X2: Crystal oscillator (main system clock)

XT1, XT2: Crystal oscillator (subsystem clock)

Specifications in this document are tentative and subject to change.

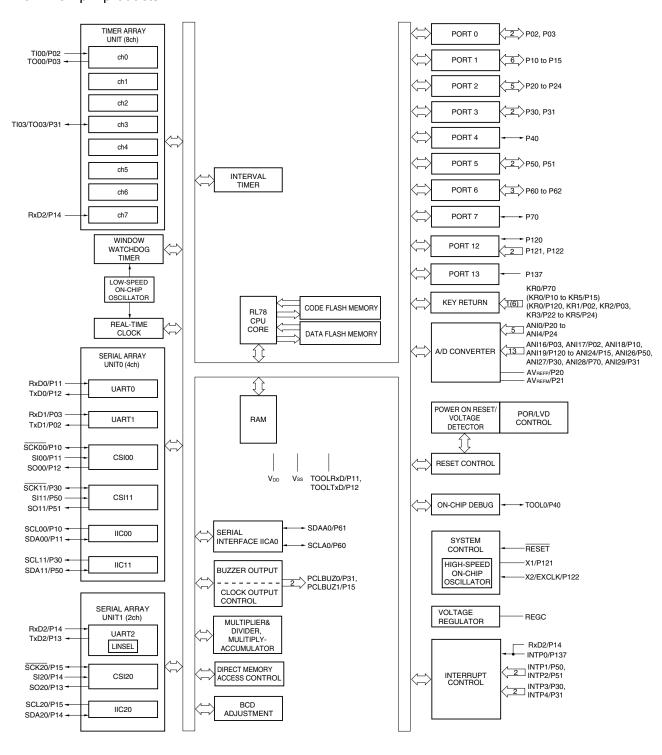
1.5 Block Diagram

1.5.1 25-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

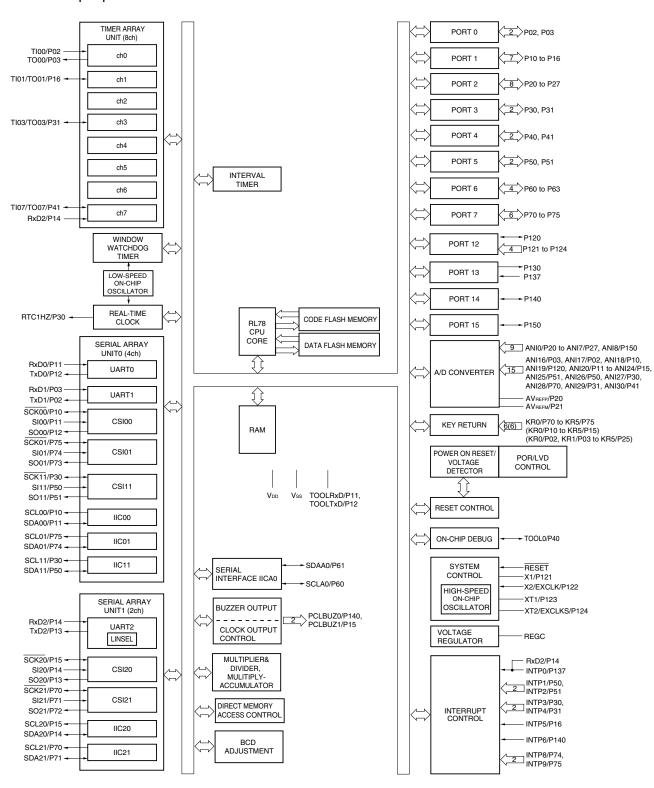
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Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

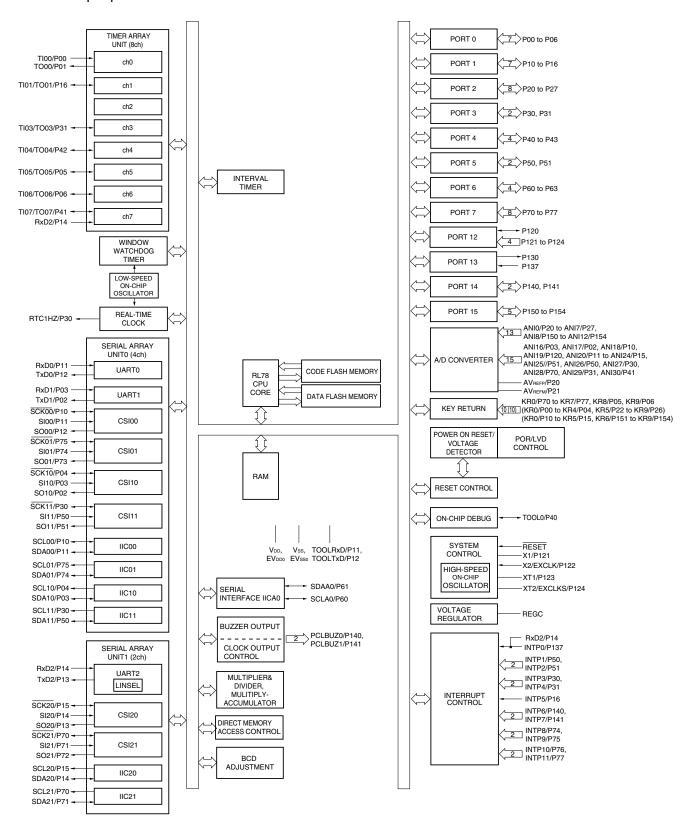
Specifications in this document are tentative and subject to change.

1.5.3 48-pin products



Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.5.4 64-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.6 Outline of Functions

(1/2)

					(1/2)		
	Item	25-pin	32-pin	48-pin	64-pin		
		R5F10E8x	R5F10EBx	R5F10EGx	R5F10ELx		
Code flash m	emory (KB)	16 to 64	16 to 64	16 to 64	32 to 64		
Data flash me	emory (KB)	4	4	4	4		
RAM (KB)		2 to 4 ^{Note1}	2 to 4 ^{Note1}	2 to 4 ^{Note1}	2 to 4 ^{Note1}		
Memory space	ce	1 MB					
Main system clock	High-speed system clock		-	stem clock input (EXCLK = 1.8 to 2.7 V, 1 to 4 MH			
	High-speed on-chip oscillator	2.4 to 3.6 V), Low-speed	High-speed operation: 1 to 32 MHz (V_{DD} = 2.7 to 3.6 V), High-speed operation: 1 to 16 MHz (2.4 to 3.6 V), Low-speed operation: 1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), Low-voltage operation: 1 MHz (V_{DD} = 1.6 to 3.6 V)				
Subsystem c	lock		_	XT1 (crystal) oscillation clock input (EXCLKS)			
				32.768 kHz (TYP.): VDD	= 1.6 to 3.6 V		
Low-speed o	n-chip oscillator	15 kHz (TYP.): V _{DD} = 1.0	6 to 3.6 V				
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)					
Minimum inst	truction execution time	0.03125 μs (High-speed	d on-chip oscillator: fin = 3	32 MHz operation)			
		0.05 μ s (High-speed sys	stem clock: fmx = 20 MHz	operation)			
			_	30.5 μ s (Subsystem clock: fsuB = 32.768 kHz operation)			
Instruction se	et	Multiplication (8 bits	r/logical operation (8/16 t \times 8 bits)	pits) reset, test, and Boolean	operation), etc.		
I/O port	Total	19	26	42	56		
	CMOS I/O	14	20	32	46		
	CMOS input	3	3	5	5		
	CMOS output	-	-	1	1		
	N-ch open-drain I/O (6 V tolerance)	2	3	4	4		
Timer	16-bit timer		8 cha	annels			
	Watchdog timer		1 ch	annel			
	Real-time clock (RTC)	-		1 ch	annel		
	Interval timer (IT)		1 ch	annel			
	Timer output	2 channels (PWM output	ts: 1 Note 2)	4 channels (PWM outputs: 3 Note 2)	7 channels (PWM outputs: 6 Note 2)		
	RTC output		=	1 • 1 Hz (subsystem clock: fsub = 32.768 kHz or)			

Notes 1. In the case of the 4 KB, this is about 3 KB when the self-programming function and data flash function are used.

2. The number of outputs varies, depending on the setting.

(2/2)

					(2/2)		
Ite	m	25-pin	32-pin	48-pin	64-pin		
		R5F10E8x	R5F10EBx	R5F10EGx	R5F10ELx		
Clock output/buzz	er output	1	2	2	2		
		2.5 MHz, 5 MHz, 10 M	 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 (Subsystem clock: fsub = 32.768 kHz operation) 				
8/12-bit resolution	A/D converter	13 channels	18 channels	24 channels	28 channels		
Serial interface		[25-pin products]					
		[32-pin products] CSI: 1 channel/UAR CSI: 1 channel/UAR CSI: 1 channel/UAR [48-pin products] CSI: 2 channels/UAR CSI: 1 channel/UAR CSI: 2 channels/UAR CSI: 2 channels/UAR CSI: 2 channels/UAR CSI: 2 channels/UAR	GI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel GI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel GI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel In products] GI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels GI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel GI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 2 channels In products] GI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels GI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels				
			1	1	1		
Multiplier and divider/multiply-ad	I ² C bus	1 channel 1 channel 1 channel 1 channel 1 channel					
		• 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)					
DMA controller		2 channels					
Vectored	Internal	24	27	27	27		
interrupt sources	External	6	6	10	13		
Key interrupt		0 ch (4 ch) Note 1	1 ch (6 ch) Note 1	6 ch	10 ch		
Reset		 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note 2 Internal reset by RAM parity error Internal reset by illegal-memory access 					
Power-on-reset ci	rcuit	Power-on-reset: 1. Power-down-reset: 1.	51 ±0.03 V 50 ±0.03 V				
Voltage detector		1.63 V to 3.06 V (12 sta	ages)				
On-chip debug fu	nction	Provided					
Power supply volt	age	V _{DD} = 1.6 to 3.6 V					
Operating ambier	t temperature	T _A = -40 to +85 °C					

- Notes 1. Can be used by the Peripheral I/O redirection register (PIOR).
 - The illegal instruction is generated when instruction code FFH is executed.
 Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS

- Cautions 1. These specifications show target values, which may change after device evaluation.
 - 2. The RL78/G1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 3. The pins mounted depend on the product. Refer to 1.3.1 25-pin products to 1.3.4 64-pin products.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25^{\circ}C$) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0}	$EV_{DD0} \leq V_{DD}$	-0.5 to +6.5	V
	AV _{DD}	$AV_{DD0} \leq V_{DD}$	-0.5 to +4.6	V
	Vss		-0.5 to +0.3	V
	EV _{SS0}		-0.5 to +0.3	V
	AVss		-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to $+2.8$ and -0.3 to V_{DD} $+0.3^{Note 1}$	V
Input voltage	VII	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	٧
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P121 to P124, P137, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
	VI4	P20 to P27, P150 to P154	-0.3 to AV _{DD} +0.3 ^{Note 3}	V
Output voltage	V ₀₁	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P63, P70 to P77, P120, P130, P140, P141	-0.3 to EV _{DD0} +0.3 ^{Note 2}	٧
	V _{O2}	P20 to P27, P150 to P154	-0.3 to V _{DD} +0.3 Note 2	V
Analog input voltage	V _{Al1}	ANI16 to ANI30	-0.3 to EV _{DD0} +0.3 Note 2	٧
	V _{Al2}	ANI0 to ANI12	-0.3 to AV _{DD} +0.3 Note 2	V

Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum ratinwg of the REGC pin. Do not use this pin with voltage applied to it.

- Must be 6.5 V or lower. 2.
- Must be 4.6 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P130, P140, P141	-40	mA
		Total of all pins -170 mA	P00 to P04, P40 to P43, P120, P130, P140, P141	-70	mA
			P05, P06, P10 to P16, P30, P31, P50, P51, P70 to P77,	-100	mA
	І ОН2	Per pin	P20 to P27, P150 to P154	-0.1	mA
		Total of all pins		-1.3	mA
Output current, low	lo _{L1} Per pin		P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P63, P70 to P77, P120, P130, P140, P141	40	mA
		Total of all pins 170 mA	P00 to P04, P40 to P43, P120, P130, P140, P141	70	mA
			P05, P06, P10 to P16, P30, P31, P50, P51, P60 to P63, P70 to P77	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P154	0.4	mA
		Total of all pins		6.4	mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	T _{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.2 Oscillator Characteristics

2.2.1 Main system clock oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Ceramic resonator	V _{SS} X1 X2	X1 clock oscillation	$2.7~V \leq V_{DD} \leq 3.6~V$	1.0		20.0	MHz
	Rd {	frequency (fx) ^{Note}	$1.8~V \leq V_{DD} < 2.7~V$	1.0		8.0	MHz
	C1 C2 7		$1.6~V \le V_{DD} < 1.8~V$	1.0		4.0	MHz
Crystal resonator		X1 clock oscillation	$2.7~V \leq V_{DD} \leq 3.6~V$	1.0		20.0	MHz
	Vss X1 X2	frequency (fx) ^{Note}	$1.8~V \leq V_{DD} < 2.7~V$	1.0		8.0	MHz
	C1= C2=		$1.6~V \le V_{DD} < 1.8~V$	1.0		4.0	MHz

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

Cautions 1. When using the X1 oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- Keep the wiring length as short as possible.
- Do not cross the wiring with the other signal lines.
- Do not route the wiring near a signal line through which a high fluctuating current flows.
- Always make the ground point of the oscillator capacitor the same potential as Vss.
- Do not ground the capacitor to a ground pattern through which a high current flows.
- Do not fetch signals from the oscillator.
- 2. Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.



2.2.2 On-chip oscillator characteristics

 $(T_A = -20 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Oscillators	Parameters	Con	ditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip	fıн	$1.8~V \leq V_{DD} \leq 3.6~V$	32 MHz selected	31.68	32.00	32.32	MHz
oscillator clock frequency Note			24 MHz selected	23.76	24.00	24.24	MHz
			16 MHz selected	15.84	16.00	16.16	MHz
			12 MHz selected	11.88	12.00	12.12	MHz
			8 MHz selected	7.92	8.00	8.08	MHz
			4 MHz selected	3.96	4.00	4.04	MHz
			1 MHz selected	0.99	1.00	1.01	MHz
		1.6 V ≤ V _{DD} < 1.8 V	32 MHz selected	30.40	32.00	33.60	MHz
			24 MHz selected	22.80	24.00	25.20	MHz
			16 MHz selected	15.20	16.00	16.80	MHz
			12 MHz selected	11.40	12.00	12.60	MHz
			8 MHz selected	7.60	8.00	8.40	MHz
			4 MHz selected	3.80	4.00	4.20	MHz
			1 MHz selected	0.95	1.00	1.05	MHz
Low-speed on-chip oscillator clock frequency	fıL			12.75	15	17.25	kHz

 $(T_A = -40 \text{ to } -20^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

(1X = -+0 to -20 0, 1.0	$A = -40 (0 - 20 C, 1.0 V \le EVDDU \le VDD \le 3.0 V, VSS = EVSSU = 0 V)$									
Oscillators	Parameters	Con	ditions	MIN.	TYP.	MAX.	Unit			
High-speed on-chip	fıн	$1.8~V \leq V_{DD} \leq 3.6~V$	32 MHz selected	31.52	32.00	32.48	MHz			
oscillator clock frequency Note			24 MHz selected	23.64	24.00	24.36	MHz			
			16 MHz selected	15.76	16.00	16.24	MHz			
			12 MHz selected	11.82	12.00	12.18	MHz			
			8 MHz selected	7.88	8.00	8.12	MHz			
		1.6 V ≤ V _{DD} < 1.8 V	4 MHz selected	3.94	4.00	4.06	MHz			
			1 MHz selected	0.985	1.00	1.015	MHz			
			32 MHz selected	30.24	32.00	33.76	MHz			
			24 MHz selected	22.68	24.00	25.32	MHz			
			16 MHz selected	15.12	16.00	16.88	MHz			
			12 MHz selected	11.34	12.00	12.66	MHz			
			8 MHz selected	7.56	8.00	8.44	MHz			
			4 MHz selected	3.78	4.00	4.22	MHz			
			1 MHz selected	0.945	1.00	1.055	MHz			
Low-speed on-chip oscillator	fiL			12.75	15	17.25	kHz			
clock frequency										

Note This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.2.3 Subsystem clock oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Resonator	Recommended Circuit	Items	Conditions	MIN.	TYP.	MAX.	Unit
Crystal resonator	Vss XT2 XT1 Rd C4 — C3 —	XT1 clock oscillation frequency (fxt) ^{Note}		32	32.768	35	kHz

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

Cautions 1. When using the XT1 oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- . Keep the wiring length as short as possible.
- Do not cross the wiring with the other signal lines.
- Do not route the wiring near a signal line through which a high fluctuating current flows.
- Always make the ground point of the oscillator capacitor the same potential as Vss.
- Do not ground the capacitor to a ground pattern through which a high current flows.
- . Do not fetch signals from the oscillator.
- 2. The XT1 oscillator is designed as a low-amplitude circuit for reducing power consumption, and is more prone to malfunction due to noise than the X1 oscillator. Particular care is therefore required with the wiring method when the XT1 clock is used.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C} + 16 \text{ V} < \text{FV}_{DD} < 3.6 \text{ V} \text{ Vss} = \text{FV}_{SSO} = 0.0 \text{ V})$

Specifications in this document are tentative and subject to change.

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P130, P140, P141	1.6 V ≤ EV _{DD0} ≤ 3.6 V			-10.0 Note 2	mA
		Total of P00 to P04, P40 to P43, P120,	$2.7~V \le EV_{DD0} \le 3.6~V$		-10.0 -5.0		mA
		P130, P140, P141	1.8 V ≤ EV _{DD0} < 2.7 V			-5.0	
		(When duty = 70% Note 3)	1.6 V ≤ EV _{DD0} < 1.8 V			-2.5	mA
		Total of P05, P06, P10 to P16, P30,	$2.7~V \leq EV_{DD0} \leq 3.6~V$			-19.0	mA
		P31, P50, P51, P70 to P77,	$1.8~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		(When duty = 70% Note 3)	$1.6~V \le EV_{DD0} < 1.8~V$			-5.0	mA
		Total of all pins (When duty = 70% ^{Note 3})	$1.6~V \le EV_{DD0} \le 3.6~V$			-29.0	mA
	І он2	Per pin for P20 to P27, P150 to P154	$1.6~V \leq AV_{DD} \leq 3.6~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$1.6~V \le AV_{DD} \le 3.6~V$			-1.3	mA

- Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDDD, VDD pins to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor is 70%.

The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(loh \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 50% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(50 \times 0.01) = -14.0$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Cautions 1. P00, P02 to P04, P10 to P15, P43, P50, P71, and P74 do not output high level in N-ch open-drain mode.
 - 2. Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV}_{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	IOL1	Per pin for P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P130, P140, P141		Will V.		20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P43,	$2.7~V \leq EV_{DD0} \leq 3.6~V$			15.0	mA
		P120, P130, P140, P141 (When duty = 70% Note 3)	$1.8~V \leq EV_{DD0} < 2.7~V$			9.0	mA
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			4.5	mA
		P31, P50, P51, P60 to P63,	$2.7~V \leq EV_{DD0} \leq 3.6~V$			35.0	mA
			$1.8~V \le EV_{DD0} < 2.7~V$			20.0	mA
		P70 to P77 (When duty = 70% Note 3)	$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			10.0	mA
		Total of all pins (When duty = 70% Note 3)				50.0	mA
	lo _{L2}	Per pin for P20 to P27, P150 to P154				0.4 Note 2	mA
		Total of all pins (When duty = 70% ^{Note 3})	$1.6~V \leq AV_{DD} \leq 3.6~V$			5.2	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso and Vss pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor is 70%.

The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$

<Example> Where n = 50% and lol = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(50 \times 0.01) = 14.0 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \ 1.6 \ \text{V} \leq \text{AV} \text{DD} \leq 3.6 \ \text{V}, \ 1.6 \ \text{V} \leq \text{EV} \text{DD0} \leq \text{VDD} \leq 3.6 \ \text{V}, \ \text{Vss} = \text{EV} \text{SS0} = 0 \ \text{V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141	Normal input buffer	0.8EV _{DD0}		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P16, P43	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}$	2.0		EV _{DD0}	V
			TTL input buffer $1.6~V \le EV_{DD0} < 3.3~V$	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P154		0.7AV _{DD}		AV _{DD}	V
	V _{IH4}	P60 to P63		0.7EV _{DD0}		6.0	V
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLK	(S, RESET	0.8V _{DD}		V _{DD}	V
Input voltage, low	V _{IL1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141	Normal input buffer	0		0.2EV _{DD0}	\
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P16, P43	TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}$	0		0.5	V
			TTL input buffer $1.6~V \le EV_{DD0} < 3.3~V$	0		0.32	V
	V _{IL3}	P20 to P27, P150 to P154		0		0.3AV _{DD}	V
	V _{IL4}	P60 to P63		0	_	0.3EVDD0	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLK	(S, RESET	0		0.2V _{DD}	V

Cautions 1. The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P43, P50, P71, and P74 is EV_{DD0}, even in the N-ch open-drain mode.

2. Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV} \text{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{EV} \text{DD} 0 \le \text{V} \text{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV} \text{sso} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77,	$2.7~V \leq EV_{\text{DD0}} \leq 3.6~V,$ $I_{\text{OH1}} = -2.0~\text{mA}$	EV _{DD0} – 0.6			V
		P120, P130, P140, P141	$\label{eq:loss_loss} \begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 3.6 \ V, \\ \\ I_{\text{OH1}} = -1.5 \ mA \end{array}$	EV _{DD0} – 0.5			V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V},$ $I_{\text{OH1}} = -1.0 \text{ mA}$	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P154	$1.6~V \le AV_{DD} \le 3.6~V,$ $I_{OH2} = -100~\mu~A$	AV _{DD} – 0.5			٧
Output voltage, low	V _{OL1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77,	$\label{eq:local_local_local} \begin{split} 2.7 \ V & \leq EV_{\text{DD0}} \leq 3.6 \ V, \\ I_{\text{OL1}} & = 3.0 \ \text{mA} \end{split}$			0.6	V
		P120, P130, P140, P141	$2.7~V \leq EV_{DD0} \leq 3.6~V,$ $I_{OL1} = 1.5~mA$			0.4	V
			$1.8~V \leq EV_{DD0} \leq 3.6~V,$ $I_{OL1} = 0.6~mA$			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $\text{IoL}_1 = 0.3 \text{ mA}$			0.4	V
	V _{OL2}	P20 to P27, P150 to P154	$1.6~V \leq AV_{DD} \leq 3.6~V,$ $I_{OL2} = 400~\mu~A$			0.4	V
	V _{OL3}	P60 to P63	$2.7~V \leq EV_{DD0} \leq 3.6~V,$ $I_{OL3} = 3.0~mA$			0.4	V
			$1.8~V \leq EV_{DD0} \leq 3.6~V,$ $I_{OL3} = 2.0~mA$			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $\text{Iol3} = 1.0 \text{ mA}$			0.4	V

- Caution 1. P00, P02 to P04, P10 to P15, P43, P50, P71, and P74 do not output high level in N-ch open-drain mode.
 - 2. Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV} \text{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{EV} \text{DD} 0 \le \text{V} \text{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV} \text{sso} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішн1	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P63, P70 to P77, P120, P140, P141	VI = EVDD0				1	μΑ
	ILIH2	P20 to P27, P137, P150 to P154, RESET	$V_I = V_{DD}$				1	μΑ
	Ішнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
	ILIH4	P20 to P27, P150 to P154	$V_I = AV_{DD}$				1	μ A
Input leakage current, low	Iuu1	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P67, P70 to P77, P120, P140, P141	VI = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P154, RESET	Vı = Vss	VI = VSS			-1	μА
	Ішз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μА
				In resonator connection			-10	μΑ
	ILIL4	P20 to P27, P150 to P154	Vı = AVss				-1	μΑ
On-chip pull-up resistance	R∪	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141	Vi = EVsso	, In input port	10	20	100	kΩ

Caution Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

Specifications in this document are tentative and subject to change.

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply current	IDD1 Note 1	Operating mode	High-speed operation Note 5	f _{IH} = 32 MHz ^{Note 3}	Basic operation	V _{DD} = 3.0 V		2.1		mA
					Normal operation	V _{DD} = 3.0 V		4.6	7.0	mA
				f _{IH} = 24 MHz ^{Note 3}	Normal operation	V _{DD} = 3.0 V		3.7	5.5	mA
				f _{IH} = 16 MHz ^{Note 3}	Normal operation	V _{DD} = 3.0 V		2.7	4.0	mA
			Low-speed	fin = 8 MHz Note 3	Normal	V _{DD} = 3.0 V		1.2	1.8	mA
			operation Note 5		operation	V _{DD} = 2.0 V		1.2	1.8	mA
			Low-voltage	fin = 4 MHz Note 3	Nomal	V _{DD} = 3.0 V		1.2	1.7	mA
			operation Note 5		operation	V _{DD} = 2.0 V		1.2	1.7	mA
			High-speed	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		3.0	4.6	mA
			operation Note 5	$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		3.2	4.8	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.9	2.7	mA
				$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		1.9	2.7	mA
			Low-speed	$f_{MX} = 8 MHz^{Note 2}$	Normal	Square wave input		1.1	1.7	mA
			operation Note 5	$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		1.1	1.7	mA
				$f_{MX} = 8 MHz^{Note 2}$	Normal	Square wave input		1.1	1.7	mA
				$V_{DD} = 2.0 \text{ V}$	operation	Resonator connection		1.1	1.7	mA
			Subsystem	fsuB = 32.768 kHz	Nomal	Square wave input		4.1		μA
			clock operation	Note 4 $T_A = -40^{\circ}C$	operation	Resonator connection		4.2		μΑ
				fsub = 32.768 kHz	Nomal	Square wave input		4.1	4.9	μA
				T _A = +25°C	operation	Resonator connection		4.2	5.0	μΑ
				fsub = 32.768 kHz	Normal	Square wave input		4.2	5.5	μ A
				Note 4 $T_A = +50^{\circ}C$	operation	Resonator connection		4.3	5.6	μΑ
				fsub = 32.768 kHz	Normal	Square wave input		4.2	6.3	μA
				Note 4	operation	Resonator connection		4.2	6.4	μA
				T _A = +70°C		1 ISSUITATION CONTINUOUS		7.0	0.4	μη
				fsub = 32.768 kHz	Normal	Square wave input		4.8	7.7	μΑ
				Note 4	operation	Resonator connection		4.9	7.8	μΑ
				T _A = +85°C						

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current (except for background operation (BGO)). However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When real-time counter and watchdog timer is stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

High speed operation: VDD = 2.7 V to 3.6 V@1 MHz to 32 MHz, VDD = 2.4 V to 3.6 V@1 MHz to 16 MHz

Low speed operation: VDD = 1.8 V to 3.6 V@1 MHz to 8 MHz Low voltage operation: VDD = 1.6 V to 3.6 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(Ta = -40 to $+85^{\circ}$ C, 1.6 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	High-speed	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 3.0 V		0.54	1.63	mA
current	Note 2	mode	operation Note 7	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 3.0 V		0.44	1.28	mA
				fih = 16 MHz Note 4	V _{DD} = 3.0 V		0.40	1.00	mA
			Low-speed	fih = 8 MHz Note 4	V _{DD} = 3.0 V		260	530	μА
			operation Note 7		V _{DD} = 2.0 V		260	530	μА
			Low-voltage	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		420	640	μА
			operation Note 7		V _{DD} = 2.0 V		420	640	μА
			High-speed	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.00	mA
			operation Note 7	$V_{DD} = 3.0 \text{ V}$	Resonator connection		0.45	1.17	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.19	0.60	mA
				$V_{DD} = 3.0 \text{ V}$	Resonator connection		0.26	0.67	mA
			Low-speed	$f_{MX} = 8 MHz^{Note 3}$	Square wave input		95	330	μΑ
			operation Note 7	$V_{DD} = 3.0 \text{ V}$	Resonator connection		145	380	μΑ
				$f_{MX} = 8 MHz^{Note 3}$	Square wave input		95	330	μA
				V _{DD} = 2.0 V	Resonator connection		145	380	μА
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25		μA
			clock operation	T _A = -40°C	Resonator connection		0.44		μА
			орегация	$f_{SUB} = 32.768 \text{ kHz}^{\text{Note 5}}$	Square wave input		0.30	0.57	μΑ
				T _A = +25°C	Resonator connection		0.49	0.76	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.33	1.17	μΑ
				T _A = +50°C	Resonator connection		0.52	1.36	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.36	1.97	μΑ
				T _A = +70°C	Resonator connection		0.55	2.16	μΑ
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.97	3.37	μA
				T _A = +85°C	Resonator connection		1.16	3.56	μA
	IDD3 ^{Note 6}	STOP	T _A = -40°C				0.18		μA
		T _A = +25°C				0.23	0.50	μA	
			T _A = +50°C			0.26	1.10	μA	
			T _A = +70°C				0.29	1.90	μΑ
			T _A = +85°C				0.90	3.30	μA

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When operating real-time clock (RTC) and setting ultra-low current consumption (AMPHS1 = 1). When high-speed on-chip oscillator and high-speed system clock are stopped. When watchdog timer is stopped. The values below the MAX. column include the leakage current.
 - 6. When high-speed on-chip oscillator, high-speed system clock, and subsystem clock are stopped. When watchdog timer is stopped. The values below the MAX. column include the leakage current.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as

High speed operation: VDD = 2.7 V to 3.6 V@1 MHz to 32 MHz, VDD = 2.4 V to 3.6 V@1 MHz to 16 MHz

Low speed operation: VDD = 1.8 V to 3.6 V@1 MHz to 8 MHz Low voltage operation: VDD = 1.6 V to 3.6 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fIH: High-speed on-chip oscillator clock frequency
 - 3. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C



 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Parameter	Symbol		Conditions	3	MIN.	TYP.	MAX.	Unit
RTC operating	IRTC Notes 1, 2	fsuB = 32.768 kHz	Real-time clock	operation		0.02		μА
current			Interval timer op	Interval timer operation				
Watchdog timer operating current	WDT Notes 2, 3	fı∟ = 15 kHz				0.22		μΑ
A/D converter	IADC Note 4	Reference power				460	1090	μА
operating current		than the internal re $AV_{DD} = 3.6 \text{ V}$	eference voltage,	ANI16 to ANI30		400	950	μΑ
		Reference power s internal reference v AVDD = 3.6 V		ANI0 to ANI12, ANI16 to ANI30		400	950	μΑ
Temperature sensor operating current	Ітмрѕ					75		μΑ
LVD operating current	ILVI Note 5					0.08		μА
BGO operating current	IBGO Note 6					2.50	12.20	mA

- Notes 1. Current flowing only to the real-time clock (excluding the operating current of the XT1 oscillator). The TYP. value of the current value of the RL78/G1A is the sum of the TYP. values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. The IDD1 and IDD2 MAX. values also include the real-time clock operating current. However, IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - 2. When high speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78/G1A is the sum of IDD1, IDD2 or IDD3 and IWDT when fCLK = fSUB when the watchdog timer operates in STOP mode.
 - 4. Current flowing only to the A/D converter. The current value of the RL78/G1A is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
 - 5. Current flowing only to the LVD circuit. The current value of the RL78/G1A is the sum of IDD1, IDD2 or IDD3 and ILVI when the LVD circuit operates in the Operating, HALT or STOP mode.
 - 6. Current flowing only to the BGO. The current value of the RL78/G1A is the sum of IDD1 or IDD2 and IBG0 when the BGO operates in an operation mode.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

- 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- 3. fclk: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is TA = 25°C

2.4 AC Characteristics

2.4.1 Basic operation

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV} \text{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{EV} \text{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV} \text{sso} = 0 \text{ V})$

Items	Symbol		Con	ditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main	High-s		$2.7 V \le V_{DD} \le 3.6 V$	0.03125		1	μS
instruction execution time)		system	main n	node	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
		clock (fmain) operation	Low vo	•	$1.6 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	0.25		1	μS
			Low-sp main n		$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	0.125		1	μS
		Subsystem coperation	lock (fs	ив)	$1.8 V \leq V_{DD} \leq 3.6 V$	28.5	30.5	31.3	μS
		In the self	High-s	peed	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	0.03125		1	μS
		programming	main n	node	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
		mode	Low vo		$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	0.25		1	μS
			Low-sp	•	$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	0.125		1	μS
External main system clock	fex	2.7 V ≤ V _{DD} ≤	3.6 V			1.0		20.0	MHz
frequency		1.8 V ≤ V _{DD} <	< 2.7 V			1.0		8.0	MHz
		1.6 V ≤ V _{DD} <	< 1.8 V			1.0		4.0	MHz
	fexs					32		35	kHz
External main system clock input	texh, texl	$2.7 \text{ V} \leq V_{DD} \leq$	≤ 3.6 V			24			ns
high-level width, low-level width		$1.8~V \le V_{DD} < 2.7~V$		60			ns		
	$1.6 \text{ V} \le \text{V}_{DD} < 1.8 \text{ V}$			120			ns		
	texhs, texhs					13.7			μS
TI00, TI01, TI03 to TI07 input high-level width, low-level width	tтін, tтіL					1/fмск+10			ns ^{Note}
TO00, TO01, TO03 to TO07	fто	High-speed r	main 2	2.7 V ≤	≤ EV _{DD0} ≤ 3.6 V			8	MHz
output frequency		mode		1.8 V ≤	≤ EV _{DD0} < 2.7 V			4	MHz
			-	1.6 V ≤	≤ EV _{DD0} < 1.8 V			2	MHz
		Low voltage main mode		1.6 V ≤	≤ EV _{DD0} ≤ 3.6 V			2	MHz
		Low-speed m	nain '	1.8 V ≤	≤ EV _{DD0} ≤ 3.6 V			4	MHz
		mode		1.6 V ≤	≤ EV _{DD0} < 1.8 V			2	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	High-speed r	main 2	2.7 V ≤	≤ EV _{DD0} ≤ 3.6 V			8	MHz
frequency		mode	-	1.8 V ≤	≤ EV _{DD0} < 2.7 V			4	MHz
				1.6 V ≤	≤ EV _{DD0} < 1.8 V			2	MHz
		Low voltage	main ·	1.8 V ≤	≤ EV _{DD0} ≤ 3.6 V			4	MHz
		mode	-	1.6 V ≤	≤ EV _{DD0} < 1.8 V			2	MHz
		Low-speed m	nain	1.8 V ≤	≤ EV _{DD0} ≤ 3.6 V			4	MHz
		mode	-	1.6 V ≤	≤ EV _{DD0} < 1.8 V			2	MHz
Interrupt input high-level width,	tinth,	INTP0		1.6 V ≤	≤ V _{DD} ≤ 3.6 V	1			μS
low-level width	t INTL	INTP1 to INT	P11	1.6 V ≤	≤ EV _{DD0} ≤ 3.6 V	1			μS
Key interrupt input low-level width	tkr	KR0 to KR9	-	1.8 V ≤	≤ EV _{DD0} ≤ 3.6 V,	250			ns
			-	1.8 V ≤	$\leq AV_{DD} \leq 3.6 V$				
			-	1.6 V ≤	≤ EV _{DD0} < 1.8 V,	1			μS
			-	1.6 V ≤	≤ AV _{DD} < 1.8 V				
RESET low-level width	trsl		l l			10			μS

(Note, Caution and Remark are listed on the next page.)



Note The following conditions are required for low voltage interface when EVDDO < VDD

 $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MIN. } 125 \text{ ns}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V} : \text{MIN. } 250 \text{ ns}$

Caution Always use AVDD pin with the same potential as the VDD pin.

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))



2.5 Peripheral Functions Characteristics

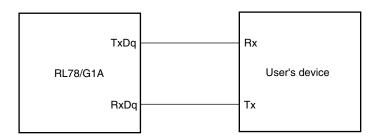
2.5.1 Serial array unit

(1) During communication at same potential (UART mode) (dedicated baud rate generator output)

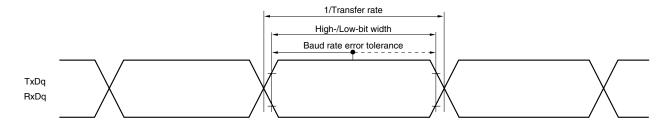
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate Note 1					fmck/6 Note 2	bps
		Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk			5.3	Mbps

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



- Notes 1. Transfer rate in the SNOOZE mode is max. 9600 bps, min. 4800 bps.
 - 2. The following conditions are required for low voltage interface when EVDDO < VDD.

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}: \text{MAX. } 2.6 \text{ Mbps}$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V}: \text{MAX. } 1.3 \text{ Mbps}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}: \text{MAX. } 0.6 \text{ Mbps}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode (fmck/2), SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	$2.7~V \leq EV_{DD0} \leq 3.6~V$	83.3 Note 1			ns
SCKp high-/low-level width	t _{KH1} , t _{KL1}	$2.7~V \leq EV_{DD0} \leq 3.6~V$	tkcy1/2 - 10			ns
SIp setup time (to SCKp↑) Note 2	tsıĸ1	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V}$	33 Note 5			ns
SIp hold time (from SCKp↑) Note 3	t _{KSI1}	$2.7~V \leq EV_{DD0} \leq 3.6~V$	10			ns
Delay time from SCKp↓ to SOp output Note 4	tkso1	C = 20 pF ^{Note 6}			10	ns

- Notes 1. The value must also be 2/fclk or more.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp1" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 5. Using the fmck within 24 MHz.
 - 6. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. This specification is valid only when CSI00's peripheral I/O redirect function is not used.
 - **2.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 1)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (master mode (fmck/4), SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C. } 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V. V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	$2.7~V \leq EV_{DD0} \leq 3.6~V$	125 Note 1			ns
		$2.4~V \leq EV_{DD0} \leq 3.6~V$	250 Note 1			ns
		1.8 V ≤ EV _{DD0} ≤ 3.6 V	500 Note 1			ns
		1.6 V ≤ EV _{DD0} ≤ 3.6 V	1000 Note 1			ns
SCKp high-/low-level width	tкн1,	$2.7~V \leq EV_{DD0} \leq 3.6~V$	tkcy1/2 - 18			ns
	t _{KL1}	$2.4~V \leq EV_{DD0} \leq 3.6~V$	tkcy1/2 - 38			ns
		1.8 V ≤ EV _{DD0} ≤ 3.6 V	tkcy1/2 - 50			ns
		1.6 V ≤ EV _{DD0} ≤ 3.6 V	tксу1/2 — 100			ns
SIp setup time (to SCKp↑) Note 2	tsıĸ1	$2.7~V \leq EV_{DD0} \leq 3.6~V$	38			ns
		$2.4~V \leq EV_{DD0} \leq 3.6~V$	75			ns
		1.8 V ≤ EV _{DD0} ≤ 3.6 V	150			ns
		1.6 V ≤ EV _{DD0} ≤ 3.6 V	300			ns
SIp hold time (from SCKp↑) Note 3	tksi1		19			ns
Delay time from SCKp↓ to SOp output Note 4	tkso1	C = 30 pF ^{Note 5}			25	ns

- Notes 1. The value must also be 4/fclk or more.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $\overline{\text{SCKp}}\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from $\overline{\text{SCKp}}\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from $\overline{SCKp}\uparrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **5.** C is the load capacitance of the \overline{SCKp} and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. This specification is valid only when CSI00's peripheral I/O redirect function is not used.
 - 2. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 2), g: PIM and POM numbers (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

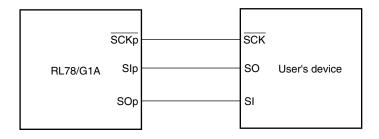
Parameter	Symbol	Conc	ditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time Note 5	tkcy2	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}$	16 MHz < fмск	8/fмск			ns
			fмск ≤ 16 MHz	6/ƒмск			ns
		1.8 V ≤ EV _{DD0} < 2.7 V	16 MHz < fмск	8/fмск			ns
			fмск ≤ 16 MHz	6/fмск			ns
		1.6 V ≤ EV _{DD0} < 1.8 V		6/fмск			ns
SCKp high-/low-level width	t _{KH2} ,	1.6 V ≤ EVDD0≤ 3.6 V	tксү2/2			ns	
SIp setup time	tsık2	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V}$	50			ns	
(to SCKp↑) Note 1		1.8 V ≤ EV _{DD0} < 2.7 V		80			ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V}$		160			ns
SIp hold time	tksi2	2.7 V ≤ EV _{DD0} ≤ 3.6 V		1/fмск+31			ns
(from SCKp↑) Note 2		1.8 V ≤ EV _{DD0} < 2.7 V	V	1/fмск+31			ns
		1.6 V ≤ EV _{DD0} < 1.8 V		1/fмск+ 250			ns
Delay time from SCKp↓ to	tkso2	C = 30 pF Note 4	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}$			2/fмск+44	ns
SOp output Note 3			2.4 V ≤ EV _{DD0} < 2.7 V			2/fмск+75	ns
			1.8 V ≤ EV _{DD0} < 2.4 V			2/fмск+110	ns
			1.6 V ≤ EV _{DD0} < 1.8 V			2/fmck+220	ns

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow^{"}$ when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from $SCKp\downarrow^{n}$ when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp1" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

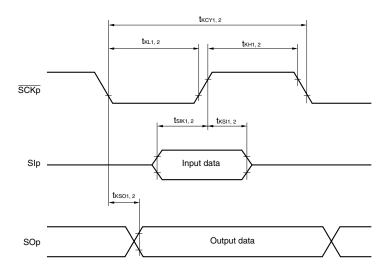
Caution Select the TTL input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 2),
 - g: PIM number (g = 0, 1)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

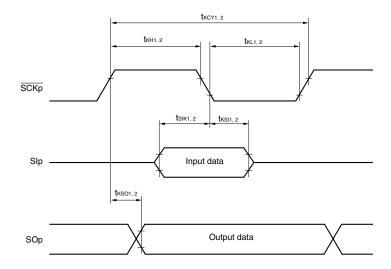
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21)

2. m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

(5) During communication at same potential (simplified I²C mode)

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$2.7~V \leq EV_{DD0} \leq 3.6~V,$		1000	kHz
		$C_b = 50$ pF, $R_b = 2.7$ k Ω			
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V},$		400	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$		300	kHz
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$			
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$		250	kHz
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V},$	475		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		1.8 V ≤ EV _{DD0} ≤ 3.6 V,	1150		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
		1.8 V ≤ EV _{DD0} < 2.7 V,	1550		ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$			
		1.6 V ≤ EV _{DD0} < 1.8 V,	1850		ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$			
Hold time when SCLr = "H"	thigh	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V},$	475		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		1.8 V ≤ EV _{DD0} ≤ 3.6 V,	1150		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$	1550		ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$			
		1.6 V ≤ EV _{DD0} < 1.8 V,	1850		ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	2.7 V ≤ EV _{DD0} ≤ 3.6 V.	1/fмск + 85		ns
, ,		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	Note		
		1.8 V ≤ EV _{DD} ≤ 3.6 V,	1/fмск + 145		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note		
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$	1/fмск + 230		ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	Note		
		1.6 V ≤ EV _{DD0} < 1.8 V,	1/fмck + 290		ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	Note		
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 3.6 \text{ V},$	0	305	ns
,		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 3.6 \text{ V},$	0	355	ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$		-	
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$	0	405	ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$		- -	
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$	0	405	ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$			

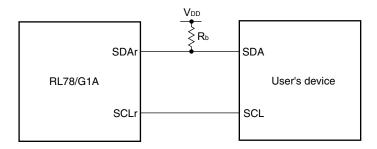
Note Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

(Caution and Remarks are listed on the next page.)

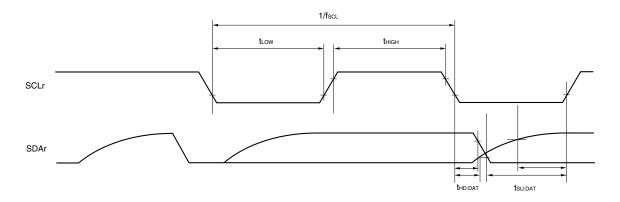


Specifications in this document are tentative and subject to change.

Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

Remarks 1. $R_b[\Omega]$:Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance

- 2. r: IIC number (r = 00, 01, 10, 11, 20, 21), g: PIM number (g = 0, 1), h: POM number (h = 0, 1)
- fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number
 (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10, 11)

(6) Communication at different potential (2.5 V) (UART mode) (dedicated baud rate generator output) (1/2) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DDO} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SSO} = 0 \text{ V})$

Parameter	Symbol		Conditions				MAX.	Unit
Transfer rate		reception	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V},$				fmck/6 ^{Note 1}	bps
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk			5.3	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$				fMCK/6 Notes 1 to 3	bps
				Theoretical value of the maximum transfer rate fclk = 8 MHz, fMck = fclk			1.3	Mbps

- Notes 1. Transfer rate in the SNOOZE mode: MAX. 9600 bps, MIN. 4800 bps
 - 2. Use it with EVDD0≥Vb.
 - 3. The following conditions are required for low voltage interface when EVDDO < VDD.

 $2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 2.7 \text{ V} : \text{MAX. } 2.6 \text{ Mbps}$ $1.8 \text{ V} \le \text{EV}_{\text{DDO}} < 2.4 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$ $1.6 \text{ V} \le \text{EV}_{\text{DDO}} < 1.8 \text{ V} : \text{MAX. } 0.6 \text{ Mbps}$

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

- n: Channel number (mn = 00 to 03, 10, 11)
- **4.** V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in UART mode.

$$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$$
: VIH = $2.0 \text{ V}, \text{VIL} = 0.5 \text{ V}$

$$1.8~V \leq EV_{\text{DD0}} < 3.3~V,~1.6~V \leq V_{\text{b}} \leq 2.0~V;~V_{\text{IH}}$$
 = $1.5~V,~V_{\text{IL}}$ = $0.32~V$

5. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (2.5 V) (UART mode) (dedicated baud rate generator output) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Parameter	Symbol		Conditions				MAX.	Unit
Transfer rate		transmission	$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 3.6 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$				Notes 1, 2	bps
				Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 2.7$ k Ω , $V_b = 2.3$ V			1.2 Note 5	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$				Notes 1, 4, 5	bps
				Theoretical value of the maximum transfer rate			0.43 Note 6	Mbps
				$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$				

- Notes 1. Transfer rate in the SNOOZE mode: MAX. 9600 bps, MIN. 4800 bps
 - 2. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 3.6 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **3.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 2 above to calculate the maximum transfer rate under conditions of the customer.
- 4. Use it with EVDD0 ≥ Vb.
- **5.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{1.5}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 7 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

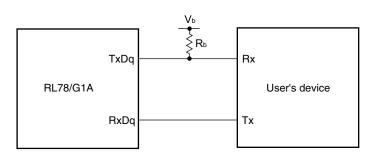
- Remarks 1. $R_b[\Omega]$:Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
 - **4.** V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in UART mode.

$$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} : \text{V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V}$$

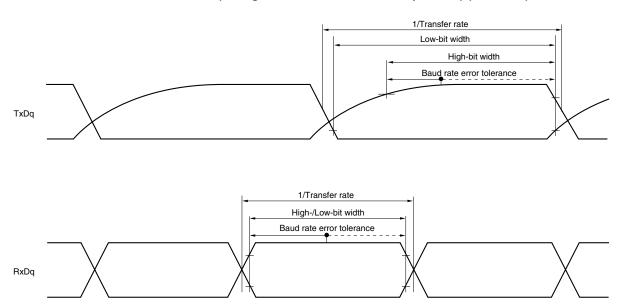
$$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} : \text{V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V}$$

5. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** UART2 cannot communicate at different potentia when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.
 - 2. $R_b[\Omega]$:Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage
 - 3. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)

(7) Communication at different potential (2.5 V) (fMck/2) (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

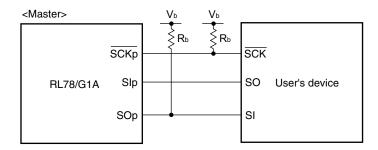
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	$2.7~V \leq EV_{DD0} < 3.6~V, 2.3~V \leq V_b \leq 2.7~V,$	300 Note 1			ns
		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
SCKp high-level width	t _{KH1}	$2.7~V \leq EV_{DD0} < 3.6~V, 2.3~V \leq V_b \leq 2.7~V,$	tkcy1/2 -			ns
		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	120			
SCKp low-level width	t _{KL1}	$\label{eq:2.7} 2.7~V \leq EV_{\text{DD0}} < 3.6~V, 2.3~V \leq V_{\text{b}} \leq 2.7~V,$	tkcy1/2 - 10			ns
		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
Slp_setup time	tsıĸı	$2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	121			ns
(to SCKp↑) Note 2		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
Slp hold time	tksi1	$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 3.6 \ V, 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \\ \end{array}$	10			ns
(from SCKp↑) Note 2		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
Delay time from SCKp↓ to	tkso1	$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 3.6 \ V, \ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \end{array}$			130	ns
SOp output Note 2		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
Slp_setup_time	tsıĸ1	$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 3.6 \ V, \ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \end{array}$	33			ns
(to SCKp↓) Note 3		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
Slp hold time	tksi1	$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 3.6 \ V, \ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \end{array}$	10			ns
(from SCKp↓) Note 3		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
Delay time from SCKp↑ to	tkso1	$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 3.6 \ V, \ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \end{array}$			10	ns
SOp output Note 3		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				

Notes 1. The value must also be 2/fclk or more.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 3. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remark are listed on the next page.)

CSI mode connection diagram (during communication at different potential)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** $R_b[\Omega]$: Communication line (\overline{SCKp} , SOp) pull-up resistance, $C_b[F]$: Communication line (\overline{SCKp} , SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)
 - 3. V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

$$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$$
: Vih = $2.0 \text{ V}, \ \text{Vil} = 0.5 \text{ V}$

4. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00)

products.

(8) Communication at different potential (2.5 V) (fmck/4) (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C. } 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V. V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	$2.7~V \leq EV_{DD0} < 3.6~V, 2.3~V \leq V_b \leq 2.7~V,$	500 Note			ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
		$1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	1150 Note			ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω				
SCKp high-level width	tкн1	$2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	tkcy1/2 -			ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	170			
		$1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	tkcy1/2 -			ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$	458			
SCKp low-level width	t _{KL1}	$2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	tkcy1/2 - 18			ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
		$1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	tксу1/2 - 50			ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				

Note The value must also be 4/fclk or more.

- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
 - 2. Use it with EVDD0 ≥ Vb.
- **Remarks 1.** $R_b[\Omega]$: Communication line (\overline{SCKp} , SOp) pull-up resistance, $C_b[F]$: Communication line (\overline{SCKp} , SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20), m: Unit number, n: Channel number (mn = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)
 - 3. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

$$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} : \text{V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V}$$

$$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} : \text{V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V}$$

4. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(8) Communication at different potential (2.5 V) (fmck/4) (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

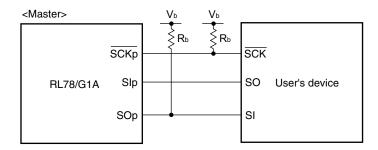
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SIp setup time	tsıĸ1	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	177			ns
(to SCKp↑) Note 1		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	479			ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				
Slp hold time	t _{KSI1}	$2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	19			ns
(from SCKp↑) Note 1		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
		$1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	19			ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				
Delay time from SCKp↓ to	tkso1	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$			195	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$			483	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				
SIp setup time	tsıĸ1	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	44			ns
(to SCKp↓) Note 2		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
		$1.8 \ V \le EV_{DD0} < 3.3 \ V, \ 1.6 \ V \le V_b \le 2.0 \ V,$	110			ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				
Slp hold time	tksi1	$2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	19			ns
$(from \overline{SCKp}_{\downarrow})^{Note 2}$		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
		$1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	19			ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				
Delay time from SCKp↑ to	tkso1	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$			25	ns
SOp output Note 2		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$				
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$			25	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Cautions and Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

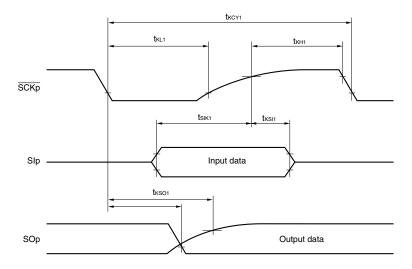


- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
 - 2. Use it with EVDD0 ≥ Vb.
- **Remarks 1.** $R_b[\Omega]$:Communication line (\overline{SCKp} , SOp) pull-up resistance, $C_b[F]$: Communication line (\overline{SCKp} , SOp) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20), m: Unit number, n: Channel number (mn = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)
 - 3. V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

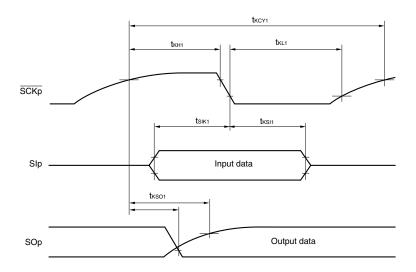
$$\begin{split} 2.7 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} \text{: V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V} \\ 1.8 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{: V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V} \end{split}$$

4. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number, n: Channel number (m = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)

2. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(9) Communication at different potential (2.5 V) (CSI mode) (slave mode, SCKp... external clock input) (Ta = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

Parameter	Symbol	C	Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time Note 1	tkcy2	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V},$	24 MHz < fмск	20/fмск			ns
		$2.3 \ V \leq V_b \leq 2.7 \ V$	20 MHz < fмcк≤ 24 MHz	16/ fмск			ns
			16 MHz < fмcк≤ 20 MHz	14/fмск			ns
			8 MHz < fмcк≤ 16 MHz	12/fмск			ns
			4 MHz < fмcк≤8 MHz	8/fмск			ns
			fмcк≤ 4 MHz	6/fмск			ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$	24 MHz < fмск	48/fмск			ns
		$1.6~V \le V_b \le 2.0~V^{\text{Note 2}}$	20 MHz < fмcк≤ 24 MHz	36/fмск			ns
			16 MHz < fмcк≤ 20 MHz	32/fмск			ns
			8 MHz < fмcк≤ 16 MHz	26/fмск			ns
			4 MHz < fмcк≤8 MHz	16/ fмск			ns
			fмcк≤ 4 MHz	10/fмск			ns
SCKp high-/low-level width	tкн2, tкL2	2.7 V ≤ EV _{DD0} < 3.6	S V, 2.3 V \leq V _b \leq 2.7 V	tkcy2/2 - 18			ns
		1.8 V ≤ EV _{DD0} < 3.3	$3~V,~1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}}$	tkcy2/2 - 50			ns
SIp setup time	tsik2	2.7 V ≤ EV _{DD0} ≤ 3.6	S V	60			ns
(to SCKp↑) Note 3		1.8 V ≤ EV _{DD0} < 3.3	3 V	97			ns
SIp hold time (from SCKp↑) Note 4	tksi2			1/fмск + 31			ns
Delay time from SCKp↓ to	tkso2	2.7 V ≤ EV _{DD0} < 3.6	$6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$			2/fмск +	ns
SOp output Note 5		$C_b = 30 \text{ pF}, R_b = 2.$	$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			214	
		$1.8~V \leq EV_{DD0} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}},$				2/fмск +	ns
		$C_b = 30 \text{ pF}, R_b = 5.$	5 kΩ			573	

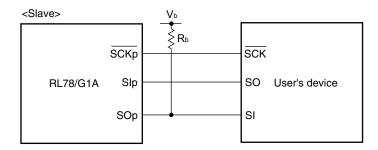
Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

- 2. Use it with $EV_{DD0} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from $\overline{\text{SCKp}}\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp1" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remarks are listed on the next page.)

Specifications in this document are tentative and subject to change.

CSI mode connection diagram (during communication at different potential)



Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

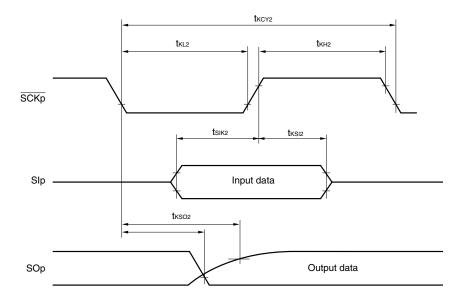
- **Remarks 1.** R_b $[\Omega]$:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10))
 - 4. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

$$\begin{split} 2.7 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} \text{: V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V} \\ 1.8 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{: V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V} \end{split}$$

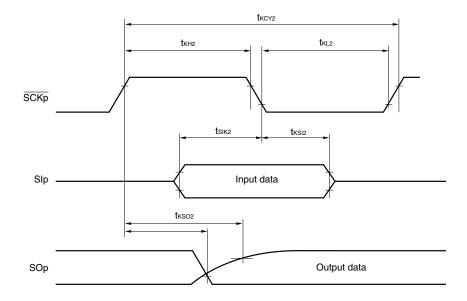
5. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Specifications in this document are tentative and subject to change.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number, n: Channel number (mn = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)

2. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(10) Communication at different potential (2.5 V) (simplified I²C mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		1000	kHz
		$\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		400	kHz
		$\begin{split} 1.8 \ V & \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V & \leq V_b \leq 2.0 \ V^{\text{Note 1}}, \\ C_b & = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		300	kHz
Hold time when SCLr = "L"	tLOW	$\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	475		ns
		$\begin{split} 2.7 \ V & \leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1150		ns
		$\begin{split} 1.8 \ V & \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V & \leq V_b \leq 2.0 \ V^{\text{Note 1}}, \\ C_b & = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	1550		ns
Hold time when SCLr = "H"	tнівн	$\begin{split} 2.7 \ V & \leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	200		ns
		$\begin{split} 2.7 \ V & \leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	600		ns
		$\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 1}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	610		ns

(Notes, Caution and Remarks are listed on the next page.)

(10) Communication at different potential (2.5 V) (simplified I²C mode) (2/2)

(Ta = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Data setup time (reception)	tsu:dat	$\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 135 Note 2		ns
	_	$ \begin{aligned} &2.7 \; V \leq EV_{DD0} \leq 3.6 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 2		ns
		$ \begin{aligned} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Notes 1}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 2		ns
Data hold time (transmission)		$\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	0	305	ns
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} \leq 3.6 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	355	ns
		$\begin{split} 1.8 \ V & \leq EV_{\rm DD0} < 3.3 \ V, \\ 1.6 \ V & \leq V_b \leq 2.0 \ V^{\text{Note 1}}, \\ C_b & = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	0	405	ns

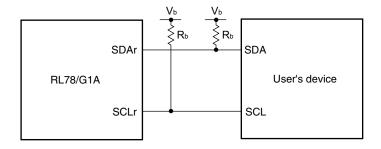
Notes 1. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg).

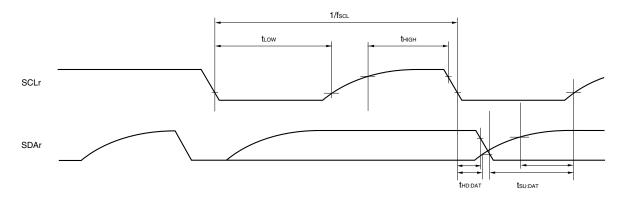
(Remarks is listed on the next page.)

^{2.} Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

- 2. r: IIC number (r = 00, 01, 10, 20), g: PIM, POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00, 01, 02, 10)
- **4.** V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in simplified I²C mode mode.

$$\begin{split} 2.7 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} \text{: V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V} \\ 1.8 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{: V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V} \end{split}$$

2.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +85^{\circ}\text{C. } 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V. V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

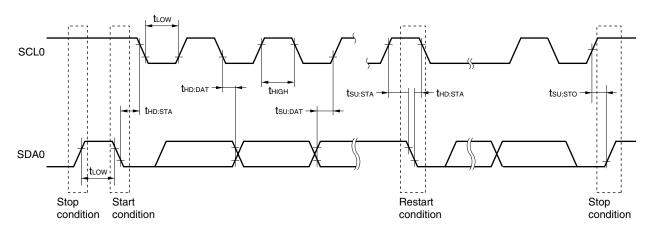
Parameter	Symbol	Conditions		Conditions Standard Mode			Fast	Mode		Mode us	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCLA0 clock frequency	fscL	Fast mode plus: fcLK≥ 10 MHz	$2.7~V \le EV_{DD0} \le 3.6~V$					0	1000	kHz	
		Fast mode: fcLk ≥ 3.5 MHz	$1.8~V \le EV_{DD0} \le 3.6~V$			0	400			kHz	
		Normal mode: fclk≥ 1 MHz	$1.6~V \le EV_{DD0} \le 3.6~V$	0	100					kHz	
Setup time of restart condition	tsu:sta			4.7		0.6		0.26		μS	
Hold time ^{Note 1}	thd:STA			4.0		0.6		0.26		μS	
Hold time when SCLA0 = "L"	tLOW			4.7		1.3		0.5		μS	
Hold time when SCLA0 = "H"	tнідн			4.0		0.6		0.26		μS	
Data setup time (reception)	tsu:dat			250		100		50		ns	
Data hold time (transmission) ^{Note 2}	thd:dat			0	3.45	0	0.9	0		μS	
Setup time of stop condition	tsu:sto			4.0		0.6		0.26		μS	
Bus-free time	tbuf			4.7		1.3		0.5		μS	

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - The maximum value (MAX.) of tho:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b=320$ pF, $R_b=1.1~k\Omega$ Fast mode plus: $C_b = 120 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



2.5.3 On-chip debug (UART)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate			115.2 k		1 M	bps

Specifications in this document are tentative and subject to change.

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

(1) When AVREF (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), AVREF (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI0 to ANI12 (supply ANI pin to AVDD)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{AV}_{DD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V}, \text{AVss} = 0 \text{ V}, \text{Reference voltage (+)} = 0.00 \text{ V}$ AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Resolution	Res		$2.4~V \le AVDD \le 3.6~V$	8	_	12	bit
			$1.8~V \le AVDD \le 3.6~V$	8		10 Note 1	
			$1.6~V \le AVDD \le 3.6~V$		8 Note 2	•	
Overall error ^{Note 3}	AINL	12-bit resolution	$2.4~V \le AVDD \le 3.6~V$			±6.0	LSB
		10-bit resolution	$1.8~V \le AVDD \le 3.6~V$			±3.5	
		8-bit resolution	$1.6~V \le AVDD \le 3.6~V$			±1.75	
Conversion time	tconv	ADTYP = 0, 12-bit resolution	$2.4~\textrm{V} \leq \textrm{Vdd} \leq 3.6~\textrm{V}$	3.375			μS
		ADTYP = 0, 10-bit resolution Note 1	$1.8~V \leq V_{DD} \leq 3.6~V$	6.75			
		ADTYP = 0, 8-bit resolution Note 2	$1.6~V \leq V_{DD} \leq 3.6~V$	13.5			
		· · · · · · · · · · · · · · · · · · ·	$2.4~V \leq V_{DD} \leq 3.6~V$	2.5625			
		8-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$	5.125			
		1.0	$1.6~\text{V} \leq \text{Vdd} \leq 3.6~\text{V}$	10.25			
Zero-scale error ^{Notes 3, 4}	EZS	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			±4.0	%FSR
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			±2.5	
		8-bit resolution	$1.6~\text{V} \leq \text{Vdd} \leq 3.6~\text{V}$			±1.25	
Full-scale error ^{Notes 3, 4}	EFS	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			±4.0	%FSR
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			±2.5	-
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			±1.25	
Integral linearity error ^{Note 3}	ILE	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			T.B.D.	LSB
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			T.B.D.	1
		8-bit resolution	$1.6~\text{V} \leq \text{Vdd} \leq 3.6~\text{V}$			T.B.D.	
Differential linearity error Note 3	DLE	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			T.B.D.	LSB
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
Reference voltage (+)	AV _{REF(+)}	= AVREFP	$2.4~V \leq V_{DD} \leq 3.6~V$	2.4		AV _{DD}	V
			$1.8~V \leq V_{DD} \leq 3.6~V$	1.8		AV _{DD}	
			$1.6~V \leq V_{DD} \leq 3.6~V$	1.6		AV _{DD}	
Reference voltage (-)	AV _{REF(-)}	= AVREFM		-0.5		0.3	٧
Analog input voltage	Vain			0		AVREFP	V
	V _{BGR}	$2.4~V \leq V_{DD} \leq 3.6~V$		1.38	1.45	1.5	V
Consumption current	IADC	AVDD = 3.6 V		460	1090	μΑ	
VREF current	IAVREF	AVREFP = 3.6 V			14	25	μΑ

Notes 1. Cannot be used for lower 2 bit of ADCR register

- Cannot be used for lower 4 bit of ADCR register
- **3.** Excludes quantization error ($\pm 1/2$ LSB).
- This value is indicated as a ratio (%FSR) to the full-scale value.



Specifications in this document are tentative and subject to change.

(2) When AVREF (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), AVREF (-) = AVSS (ADREFM = 0), target ANI pin : ANIO to ANI12 (supply ANI pin to AVDD)

(TA = -40 to +85°C, 1.6 V \leq VDD \leq 3.6 V, 1.6 V \leq AVDD \leq 3.6 V, Vss = 0 V, AVss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
Resolution	Res		$2.4~V \le AV_{DD} \le 3.6~V$	8		12	bit
			$1.8~V \le AV_{DD} \le 3.6~V$	8		10 Note 1	
			$1.6~V \le AV_{DD} \le 3.6~V$		8 Note 2		
Overall error ^{Note 3}	AINL	12-bit resolution	$2.4~V \le AV_{DD} \le 3.6~V$			±9.0	LSB
		10-bit resolution	$1.8~V \le AVDD \le 3.6~V$			±5.0	
		8-bit resolution	$1.6~V \le AVDD \le 3.6~V$			±2.5	
Conversion time	tconv	ADTYP = 0, 12-bit resolution	$2.4~V \leq V \text{DD} \leq 3.6~V$	3.375			μS
		ADTYP = 0, 10-bit resolution Note 1	$1.8~V \leq V \text{DD} \leq 3.6~V$	6.75			
		ADTYP = 0, 8-bit resolution Note 2	$1.6~V \leq V \text{DD} \leq 3.6~V$	13.5			
		ADTYP = 1,	$2.4~V \leq V_{DD} \leq 3.6~V$	2.5625			
		8-bit resolution	1.8 V ≤ VDD ≤ 3.6 V	5.125			
			$1.6~V \leq V_{DD} \leq 3.6~V$	10.25			
Zero-scale error ^{Notes 3, 4}	EZS	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			±7.0	%FSR
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			±3.75	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			±2.0	
Full-scale error ^{Notes 3, 4}	EFS	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			±7.0	%FSR
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			±3.75	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			±2.0	
Integral linearity error ^{Note 3}	ILE	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			T.B.D.	LSB
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
Differential linearity error Note 3	DLE	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			T.B.D.	LSB
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
Reference voltage (+)	AVREFP	= AVDD		1.6		3.6	V
Reference voltage (-)	AVREFM	= AVss		-0.5		0.3	V
Analog input voltage	VAIN			0		AVREFP	V
	V _{BGR}	$2.4~V \leq V_{DD} \leq 3.6~V$		1.38	1.45	1.5	V
Consumption current	IADC	AVDD = 3.6 V		460	1090	μΑ	
V _{REF} current	IAVREF	AVREFP = 3.6 V			14	25	μΑ

- Notes 1. Cannot be used for lower 2 bit of ADCR register
 - Cannot be used for lower 4 bit of ADCR register
 - Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.



(3) When AVREF (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), AVREF (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI16 to ANI30 (supply ANI pin to EVDDO)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \ 1.6 \text{ V} \le \text{EV}_{\text{DD}} \le \text{V}_{\text{DD}} \le 3.6 \text{ V}, \ 1.6 \text{ V} \le \text{AV}_{\text{DD}} \le 3.6 \text{ V}, \ \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = 0 \text{ V}, \ \text{AV}_{\text{SS}} = 0 \text{ V}, \ \text{Reference}$ voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
Resolution	Res		$2.4~V \leq AV_{DD} \leq 3.6~V$	8		12	bit
			$1.8~V \leq AV_{DD} \leq 3.6~V$	8		10 Note 1	
			$1.6~V \le AV_{DD} \le 3.6~V$		8 Note 2		
Overall error ^{Note 3}	AINL	12-bit resolution	$2.4~V \le AV_{DD} \le 3.6~V$			±9.0	LSB
		10-bit resolution	$1.8~V \le AVDD \le 3.6~V$			±5.0	
		8-bit resolution	$1.6~V \le AV_{DD} \le 3.6~V$			±2.5	
Conversion time	tconv	ADTYP = 0, 12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$	4.125			μS
		ADTYP = 0, 10-bit resolution Note 1	$1.8~V \leq V_{DD} \leq 3.6~V$	9.5			
		ADTYP = 0, 8-bit resolution Note 2	$1.6~V \leq V \text{DD} \leq 3.6~V$	57.5			
		ADTYP = 1, 2	$2.4~V \leq V_{DD} \leq 3.6~V$	3.3125			
		8-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$	7.875			
			$1.6~V \leq V_{DD} \leq 3.6~V$	54.25			
Zero-scale error ^{Notes 3, 4}	EZS	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			±7.0	%FSR
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			±3.75	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			±2.0	
Full-scale error ^{Notes 3, 4}	EFS	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			±7.0	%FSR
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			±3.75	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			±2.0	
Integral linearity error ^{Note 3}	ILE	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			T.B.D.	LSB
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
Differential linearity error Note 3	DLE	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			T.B.D.	LSB
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
Reference voltage (+)	AV _{REF(+)}	= AVREFP	$2.4~V \leq V_{DD} \leq 3.6~V$	2.4		AV _{DD}	V
			$1.8~V \leq V_{DD} \leq 3.6~V$	1.8		AV _{DD}	
			$1.6~V \leq V_{DD} \leq 3.6~V$	1.6		AV _{DD}	
Reference voltage (-)	AV _{REF((-)}	= AVREFM		-0.5		0.3	٧
Analog input voltage	Vain			0		AVREFP	٧
	V _{BGR}	2.4 V ≤ VDD ≤ 3.6 V		1.38	1.45	1.5	٧
Consumption current	IADC	AVDD = 3.6 V		400	950	μА	
V _{REF} current	IAVREF	AVREFP = 3.6 V			14	25	μΑ

Notes 1. Cannot be used for lower 2 bit of ADCR register

- 2. Cannot be used for lower 4 bit of ADCR register
- **3.** Excludes quantization error ($\pm 1/2$ LSB).
- This value is indicated as a ratio (%FSR) to the full-scale value.



2. ELECTRICAL SPECIFICATIONS

Caution The pins mounted depend on the product. Refer to 1.3.1 25-pin products to 1.3.4 64-pin products.

Specifications in this document are tentative and subject to change.

(4) When AVREF (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), AVREF (-) = AVSS (ADREFM = 0), target ANI pin : ANI16 to ANI30 (supply ANI pin to EVDDO)

 $(T_{\text{A}} = -40 \text{ to } +85^{\circ}\text{C}, \ 1.6 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq \text{V}_{\text{DD0}} \leq 3.6 \ \text{V}, \ 1.6 \ \text{V} \leq \text{AV}_{\text{DD}} \leq 3.6 \ \text{V}, \ \text{Vss} = \text{EV}_{\text{SS0}} = 0 \ \text{V}, \ \text{AVss} = 0 \ \text{V}, \ \text{Reference} = 0 \ \text{V}$ voltage (+) = AVDD, Reference voltage (-) = AVSS = 0 V)

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
Resolution	Res		$2.4~V \le AV_{DD} \le 3.6~V$	8		12	bit
			$1.8~V \le AV_{DD} \le 3.6~V$	8		10 Note 1	
			1.6 V ≤ AVDD ≤ 3.6 V		8 Note 2		
Overall error ^{Note 3}	AINL	12-bit resolution	$2.4~V \le AV_{DD} \le 3.6~V$			±14.0	LSB
		10-bit resolution	$1.8~V \le AVDD \le 3.6~V$			±7.5	
		8-bit resolution	$1.6~V \le AVDD \le 3.6~V$			±3.75	
Conversion time	tconv	ADTYP = 0, 12-bit resolution	$2.4~V \leq V \text{DD} \leq 3.6~V$	4.125			μS
		ADTYP = 0, 10-bit resolution Note 1	$1.8~V \leq V \text{DD} \leq 3.6~V$	9.5			
		ADTYP = 0, 8-bit resolution Note 2	$1.6~V \leq V \text{DD} \leq 3.6~V$	57.5			
		ADTYP = 1,	$2.4~V \leq V_{DD} \leq 3.6~V$	3.3125			μS
		8-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$	7.875			
			$1.6~V \leq V_{DD} \leq 3.6~V$	54.25			
Zero-scale error ^{Notes 3, 4}	EZS	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			±9.0	%FSR
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			±5.0	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			±2.5	
Full-scale error ^{Notes 3, 4}	EFS	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			±9.0	%FSR
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			±5.0	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			±2.5	
Integral linearity error ^{Note 3}	ILE	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			T.B.D.	LSB
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
Differential linearity error Note 3	DLE	12-bit resolution	$2.4~V \leq V_{DD} \leq 3.6~V$			T.B.D.	LSB
		10-bit resolution	$1.8~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
		8-bit resolution	$1.6~V \leq V_{DD} \leq 3.6~V$			T.B.D.	
Reference voltage (+)	AV _{REF(+)}	= AVDD		1.6		3.6	V
Reference voltage (-)	AVREF(-)	= AVss		-0.5		0.3	V
Analog input voltage	nput voltage Vain			0		AVREFP	V
	V _{BGR}	2.4 V ≤ VDD ≤ 3.6 V		1.38	1.45	1.5	V
Consumption current	IADC	AVDD = 3.6 V		400	950	μΑ	
VREF current	lavref	AVREFP = 3.6 V			14	25	μΑ

- Notes 1. Cannot be used for lower 2 bit of ADCR register
 - 2. Cannot be used for lower 4 bit of ADCR register
 - Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.



(5) When AVREF (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), AVREF (-) = AVss (ADREFM = 0), target ANI pin : ANI0 to ANI12, ANI16 to ANI30

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 3.6 V, 1.6 V \leq AVDD \leq 3.6 V, Vss = EVss0 = 0 V, AVss0 = 0 V, Reference voltage (+) = Internal reference voltage, Reference voltage (-) = AVss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv	8-bit resolution	16		μS	
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution			±2.5	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			T.B.D.	LSB
Differential linearity error Note 1	DLE	8-bit resolution			T.B.D.	LSB
Reference voltage (+)	AV _{REF(+)}	= Internal reference voltage	1.38	1.45	1.5	٧
Reference voltage (-)	AV _{REF(-)}	= AVss	-0.5		0.3	٧
Analog input voltage	VAIN		0		AVREFP	٧
	V _{BGR}		Conversion prohibit			V
Consumption current	IADC	AVDD = 3.6 V		400	950	μΑ
VREF current	lavref			75		μΑ

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

^{2.} This value is indicated as a ratio (%FSR) to the full-scale value.

2.6.2 Temperature sensor characteristics

(Ta = -40 to +85°C, 2.4 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, Ta = +25°C		1.05		٧
Reference output voltage	VCONST	Setting ADS register = 81H	1.38	1.45	1.5	٧
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp				2	μS

2.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.48	1.51	1.54	٧
	V _{PDR}	Power supply fall time	1.47	1.50	1.53	٧
Minimum pulse width	T _{PW}		300			μS
Detection delay time					350	μS

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(Ta = -40 to +85°C, VPDR \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _{LVD2}	Power supply rise time	3.07	3.13	3.19	V
voltage			Power supply fall time	3.00	3.06	3.12	V
		V _{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V _{LVD4}	Power supply rise time	2.86	2.92	2.97	٧
			Power supply fall time	2.80	2.86	2.91	V
		V _{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	٧
		V _{LVD6}	Power supply rise time	2.66	2.71	2.76	٧
			Power supply fall time	2.60	2.65	2.70	V
		V LVD7	Power supply rise time	2.56	2.61	2.66	٧
			Power supply fall time	2.50	2.55	2.60	V
		V _{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		V _{LVD9}	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		V _{LVD10}	Power supply rise time	1.94	1.98	2.02	٧
			Power supply fall time	1.90	1.94	1.98	V
		V _{LVD11}	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		V _{LVD12}	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		V _{LVD13}	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pu	ulse width	tLW		300			μS
Detection d	elay time					300	μS

Remark $V_{LVD(n-1)} > V_{LVDn}$: n = 3 to 13



LVD Detection Voltage of Interrupt & Reset Mode

(Ta = -40 to +85°C, VPDR \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVD13}	VPOC0,	VPOC1, VPOC2 = 0, 0, 0,	, falling reset voltage: 1.6 V	1.60	1.63	1.66	>
mode	V _{LVD12}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	٧
			(+0.1 V)	Falling interrupt voltage	1.70	1.73	1.77	٧
	V _{LVD11}		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	٧
			(+0.2 V)	Falling interrupt voltage	1.80	1.84	1.87	٧
	V _{LVD4}		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	>
			(+1.2 V)	Falling interrupt voltage	2.80	2.86	2.91	>
	V _{LVD11}	VPOC0,	VPOC1, VPOC2 = 0, 0, 1,	, falling reset voltage: 1.8 V	1.80	1.84	1.87	٧
	V _{LVD10}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	٧
			(+0.1 V)	Falling interrupt voltage	1.90	1.94	1.98	٧
	V _{LVD9}		(.00)	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	٧
	V _{LVD2}		L(12)()	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	٧
	V _{LVD8}	VPOC0,	VPOC1, VPOC2 = 0, 1, 0,	, falling reset voltage: 2.4 V	2.40	2.45	2.50	٧
	V _{LVD7}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	>
			(+0.1 V)	Falling interrupt voltage	2.50	2.55	2.60	>
	V _{LVD6}		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			(+0.2 V)	Falling interrupt voltage	2.60	2.65	2.70	>
	V _{LVD5}	VPOCO,	VPOC1, VPOC2 = 0, 1, 1,	, falling reset voltage: 2.7 V	2.70	2.75	2.81	٧
	V _{LVD4}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	٧
			(+0.1 V)	Falling interrupt voltage	2.80	2.86	2.91	٧
	V _{LVD3} L		Rising release reset voltage	2.96	3.02	3.08	V	
			(+0.2 V)	Falling interrupt voltage	2.90	2.96	3.02	٧

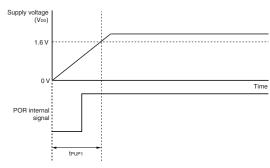
Supply Voltage Rise Time ($T_A = -40 \text{ to } +85^{\circ}\text{C}$, $V_{SS} = 0 \text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Maximum time to rise to 1.6 V (V _{DD} (MIN.)) ^{Note} (V _{DD} : 0 V \rightarrow 1.6 V)	tpup1	When RESET input is not used			3.2	ms

Note Make sure to raise the power supply in a shorter time than this.

Supply Voltage Rise Time Timing

• When RESET pin input is not used

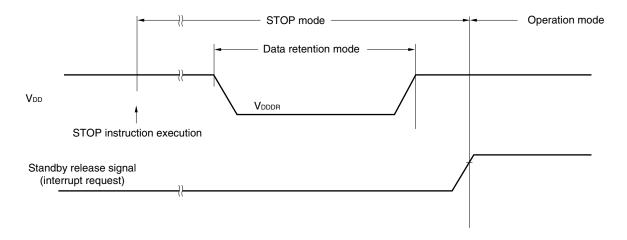


2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.47 ^{Note}		3.6	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

(1A = -40 to +65 C, 1.6 V \(\) EVDDU \(\) VDD \(\) S.6 V, VSS \(\) EVSSU \(\) V							
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$1.8~V \leq V_{DD} \leq 3.6~V$		1		32	MHz
Number of code flash rewrites	Cerwr	1 erase + 1 write after the erase is regarded as 1 rewrite.	Retained for 20 years (Self/serial programming) Note	1,000			Times
Number of data flash rewrites		The retaining years are until next rewrite after the rewrite.	Retained for 1 years (Self/serial programming) Note		1,000,000		
			Retained for 5 years (Self/serial programming) Note	100,000			

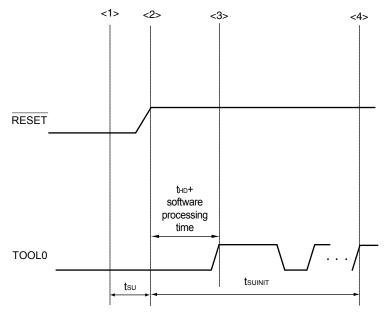
Note When using flash memory programmer and Renesas Electronics self programming library

Remark When updating data multiple times, use the flash memory as one for updating data.

2.9 Timing Specs for Switching Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when a pin reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the pin reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until a pin reset ends	tsu	POR and LVD reset must end before the pin reset ends.	10			μS
How long the TOOL0 pin must be kept at the low level after a reset ends	tно	POR and LVD reset must end before the pin reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The pins reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external and internal resets end.

How long from when the TOOL0 pin is placed at the low level until a pin reset ends tsu:

How long to keep the TOOL0 pin at the low level from when the external and internal resets end tHD:

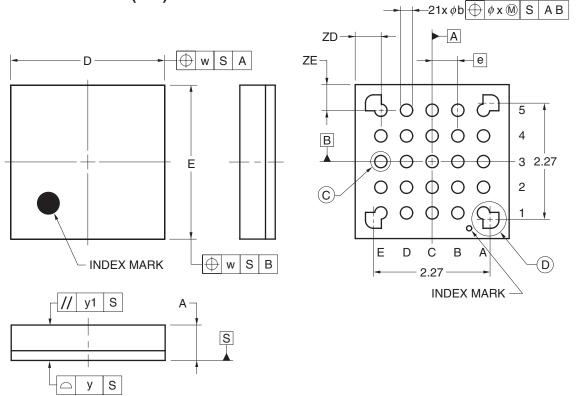
3. PACKAGE DRAWINGS

3.1 25-pin products

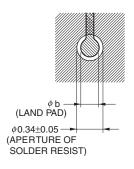
R5F10E8AALA, R5F10E8CALA, R5F10E8DALA, R5F10E8EALA

Specifications in this document are tentative and subject to change.

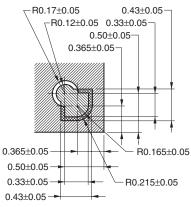
25-PIN PLASTIC FLGA (3x3)



DETAIL OF © PART



DETAIL OF (D) PART



	(UNIT:mm)
ITEM	DIMENSIONS
D	3.00±0.10
Е	3.00±0.10
W	0.20
е	0.50
A	0.69±0.07
b	0.24±0.05
х	0.05
у	0.08
y1	0.20
ZD	0.50
ZE	0.50
	P25FC-50-2N2-1

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D2

ITEM

EXPOSED DIE PAD VARIATIONS E2

MIN NOM MAX MIN NOM MAX

3.45 3.50 3.55 3.45 3.50 3.55

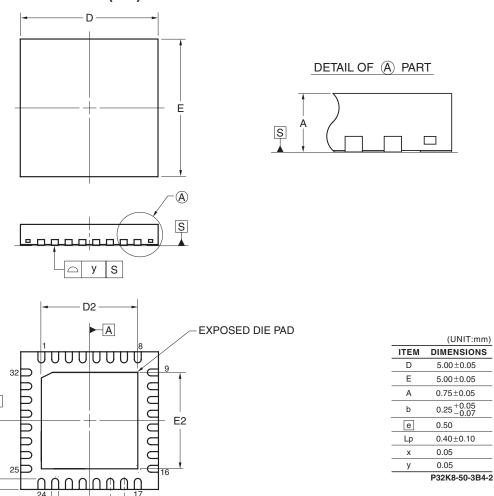
3.2 32-pin products

R5F10EBAANA, R5F10EBCANA, R5F10EBDANA, R5F10EBEANA

b x M S A B

Specifications in this document are tentative and subject to change.

32-PIN PLASTIC WQFN(5x5)



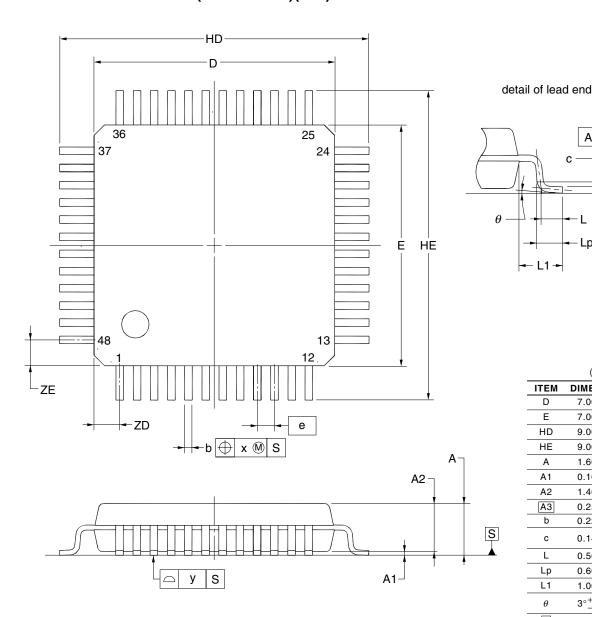
АЗ

3.3 48-pin products

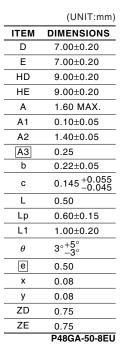
R5F10EGAAFB, R5F10EGCAFB, R5F10EGDAFB, R5F10EGEAFB

Specifications in this document are tentative and subject to change.

48-PIN PLASTIC LQFP (FINE PITCH)(7x7)

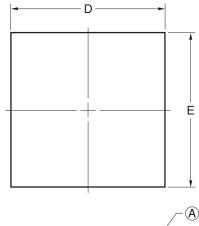


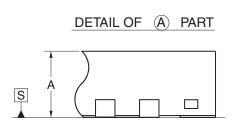
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

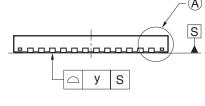


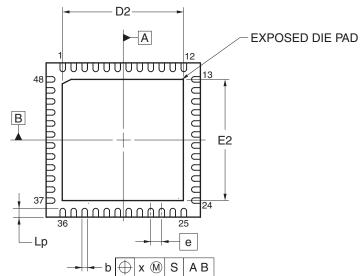
R5F10EGAANA, R5F10EGCANA, R5F10EGDANA, R5F10EGEANA

48-PIN PLASTIC WQFN(7x7)









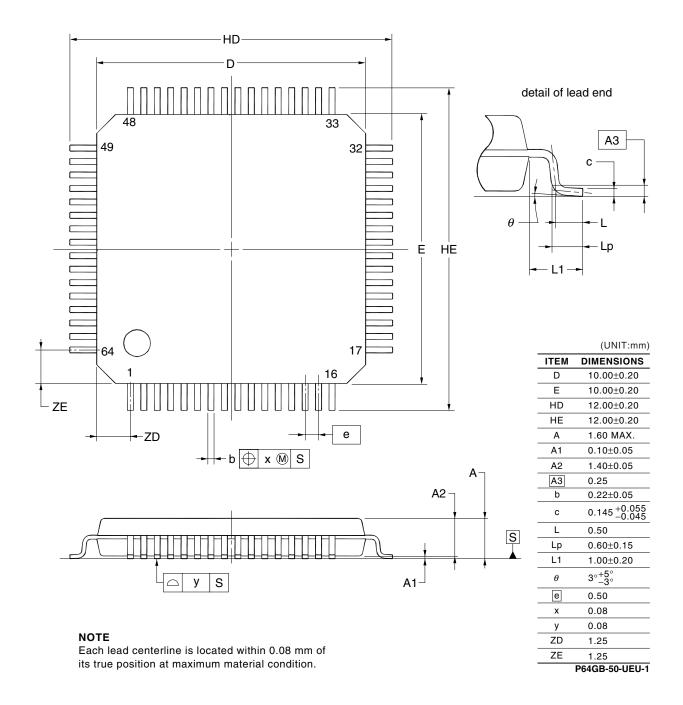
	(UNIT:mm)
ITEM	DIMENSIONS
D	7.00 ± 0.05
Е	7.00 ± 0.05
Α	0.75±0.05
b	0.25 ^{+0.05} -0.07
е	0.50
Lp	0.40±0.10
х	0.05
у	0.05
	P48K8-50-5B4-3

ITEM		D2			E2		
		MIN	NOM	MAX	MIN	MOM	MAX
EXPOSED DIE PAD VARIATIONS	Α	5.45	5.50	5.55	5.45	5.50	5.55

3.4 64-pin products

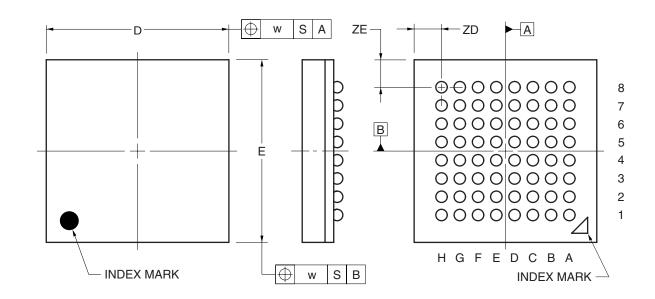
R5F10ELCAFB, R5F10ELDAFB, R5F10ELEAFB

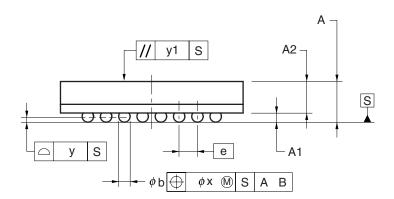
64-PIN PLASTIC LQFP(FINE PITCH)(10x10)



R5F10ELCABG, R5F10ELDABG, R5F10ELEABG

64-PIN PLASTIC FBGA (4x4)





	(UNIT:mm)
ITEM	DIMENSIONS
D	4.00±0.10
Е	4.00±0.10
W	0.15
Α	0.89±0.10
A1	0.20±0.05
A2	0.69
е	0.40
b	0.25±0.05
х	0.05
у	0.08
y1	0.20
ZD	0.60
ZE	0.60
	P64F1-40-AA2-1

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Revision History RL78/G1A Data Sheet

		Description		
Rev.	Date	Page	Summary	
0.01	Dec 26, 2011	-	First Edition issued	

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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